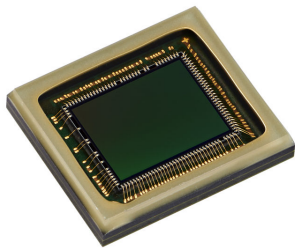
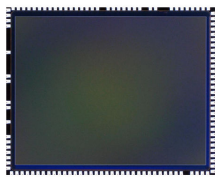
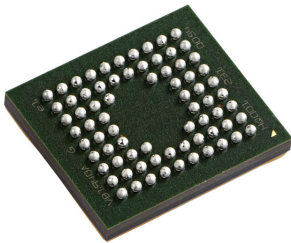


RGB-NIR 5.1 megapixel image sensor with combined global shutter and rolling shutter modes for consumer and industrial applications



VB1943



VD1943

Product	Description
VB1943	OBGA
VD1943	Bare die

Features

- **Resolution:** 5.1 megapixel sensor (2560 x 1984)
- **Chroma:** RGB-NIR, NIR or Bayer
- **Optical format:** 1/2.5 inch
- **Image array size:** 5.8 mm x 4.5 mm
- **Pixel technology:**
 - 3D stacked sensor with 2.25 μm x 2.25 μm BSI pixel size
 - Global and rolling shutter technology
- **Functions:**
 - Dual and single exposure modes with separated controls of RGB pixels and NIR pixels
 - Automatic/external synchronization mode
 - Independent horizontal and vertical image flip
 - Automatic dark calibration
 - Dynamic defective pixel correction
 - Integrated noise reduction feature
- **Advanced image processing:**
 - Embedded 18-bit high dynamic range pixel reconstruction
 - Embedded Bayer reconstruction with NIR depollution
 - Embedded NIR smart upscale to full resolution monochrome output
 - Four programmable contexts with versatile sequencing management
- **Frame rates:**
 - Up to 100 frames per second at full resolution in global shutter mode
 - Up to 50 frames per second at full resolution in rolling shutter mode
- **Interfaces:**
 - MIPI CSI-2 interface (dual/quad lanes, max. 1.5 Gbps/lane)
 - MIPI CCI control interface up to 1 MHz
 - 4 programmable GPIOs (general-purpose input/output) to control external illuminators:
 - Output is synchronized with sensor integration periods
 - PWM (pulse-width modulation) control
- Additional features: Integrated temperature sensor
- **Package options:**
 - Available as bare die
 - Available in OBGA package
- **OBGA package:**
 - Package size: 10.3 x 8.9 mm
 - Ball matrix: 10 x 9 balls, pitch 0.8 mm

Description

The VB1943 and VD1943 are 5.1 megapixel, 2.25 μm global, and rolling shutter image sensors. They are designed for a wide spectrum of applications that require capturing color and NIR images. Operation of these sensors combines global and rolling shutter technology with an extended dynamic range.

Leveraging from preeminent 3D stacking and ST patented processes, these sensors perform outstandingly in the NIR (940 nm) and visible region. In global shutter mode, they can capture up to 100 frames per second in a 2560 x 1984 resolution format.

The VB1943 and VD1943 sensors can be used in rolling shutter mode, taking advantage of low dark noise capability. They can operate in an 18-bit HDR mode compressed down to 12 or 10 bits through a customizable PWL.

The RGB-NIR input image is processed by the integrated advanced ISP. It can reconstruct a full resolution NIR smart upscaled monochrome image or a 2x2 color Bayer image NIR depolluted.

For computer vision applications, acquisition can be switched to global shutter mode with an NIR light source. Switching to global shutter mode with an external NIR light source greatly reduces the system power consumption that is required to drive the illumination.

1 Product overview

1.1 Product characteristics

Table 1. Key characteristics

Category	Parameter	Characteristics
Shutter	Type	Global Shutter (GS) and Rolling Shutter (RS)
Resolution	Pixel resolution	2560 x 1984 (5.1MP)
Pixel	Sensor technology	3D stacked BSI pixel
	Pixel size	2.25 μm x 2.25 μm
Optical characteristics	Image array size [H x V]	5.8 mm x 4.5 mm
	Optical format	1/2.5 inch
	Chief ray angle	Linear shift 20° max at 3.6 mm diagonal
	Color filter array	RGB-NIR in a 4x4 kernel
Package OBGA	Package type	OBGA
	Package dimensions	10.3 mm x 8.9 mm
	Ball pitch	0.8 mm
	Ball array	10 x 9 balls
Wafer reconstruction	Silicon die size	6546 x 5349 μm
Communication interface	Sensor data interface	MIPI CSI-2, dual or quad lanes
		300 Mbps - 1.5 Gbps
	Sensor control interface	I ² C up to 1 MHz
Output format	Pixel output format SDR	GS operation: RAW10 / RAW8 RS operation: RAW12 / RAW10 / RAW8
	Pixel output format HDR (after compression)	RS operation only: RAW12 / RAW10
Operating conditions	Supply voltages	2.8 V analog (VANA)
		1.15 V digital core (VCORE)
		1.8 V digital I/O (VDDIO)
	External clock frequency range	12 MHz to 50 MHz
	Junction temperature range (Tj)	-30°C to +85°C functional

Prerelease product(s)

Table 2. Key features

Category	Embedded features
Common control	Analog gains: x1 to x4
	Digital gains: x1 to x32
	4 programmable GPIOs
	Thermal sensors
Readout control	Cropping NIR subsampling
	Mirror/Flip
	Test pattern generation
Synchronization	Leader mode
	Follower mode with configurable GPIO input
	Exposure strobe output signal in GS mode
	MIPI readout VSYNC output signal
	Programmable delays
	Start of exposure output signal
Image processing	Automatic dark calibration
	Noise reduction
	Dynamic defective pixel correction
	Pedestal adjustment
Advanced features	Embedded Bayer reconstruction with NIR depollution (5.1 MP Bayer RGB)
	NIR smart upscale (5.1 MP NIR)
	Output pattern: <ul style="list-style-type: none"> • Monochrome NIR (optional smart upscaling) • RGB-NIR • RGB Bayer
	Context management: <ul style="list-style-type: none"> • up to 4 contexts • configurable switching sequence
	NIR pixel split exposure
	Histograms and statistics on programmable region

Table 3. Typical product performances

The product performances are provided at Tj = 60°C.

Parameter		Performances	
		Global shutter	Rolling shutter
Dynamic range (SDR)		Up to 62 dB	Up to 69 dB
Dynamic range (HDR)		NA	Up to 100 dB
Modulation transfer function at 940 nm		Nyquist: 0.50	
		Nyquist/2: 0.70	
VB1943 Peak QE	NIR (940 nm)	23%	
	Red	67%	
	Green	74%	
	Blue	62%	
VD1943 Peak QE	NIR (940 nm)	23%	
	Red	69%	
	Green	75%	
	Blue	63%	
Fixed pattern noise		3.5 e-	1.1 e-
Temporal noise		5 e-	2 e-
Max frame rate	Full resolution	100 fps	50 fps
Power consumption		60 fps NIR: 354 mW	50 fps Bayer RGB: 376 mW

Prerelease product(s)

1.2 Functional description summary

The VB1943 and VD1943 is a compact global and rolling shutter image sensor featuring an RGB-NIR matrix of 2560 x 1984 pixels.

With its global shutter operation, all pixels are synchronized to capture light at the same time. Once the integration time is completed for the whole matrix, each pixel information is transferred to a storage node, before being read and digitized rows after rows with a 10-bit ADC. This feature gets rid of the motion blur and is optimal for applications with NIR active illumination system, minimizing NIR power budget.

With its rolling shutter operation, the exposure of pixels is done sequentially, row by row. It is digitalized via a 12-bit ADC. The lower dark noise in rolling shutter mode provides an improved image quality. There is no GPIO support for driving illumination systems in rolling shutter mode.

In rolling shutter mode, the sensor also offers HDR feature by combining two consecutive exposures with different durations in the same frame. A FIFO buffers the pixel conversion result of the first exposure. The HDR merge block combines data coming from FIFO (first exposure) and the pixel digitalization of the second exposure, then generates the HDR image. The ratio of exposure can be up to 64, providing 18-bit resolution images.

The RGB-NIR image input stream goes through the internal ISP where dark level subtraction, digital gain, pedestal, pixel correction, noise reduction, image histograms, and statistics are applied.

The output stream can be the RGB-NIR input image, but to fit ISPs of conventional application hosts, the sensor can reconstruct and transmit a color Bayer image depolluted from NIR content. It can also extract and transmit the NIR pixels only as gray scale, smart upsampled to the input image size.

The images are output as frames of RAW8, RAW10, or RAW12 data through a MIPI CSI-2 scalable to two or four data lanes. When the output resolution is not the native ADC resolution (10 bit for global shutter or 12 bit for rolling shutter), the image is compressed following a 32 points PWL curve.

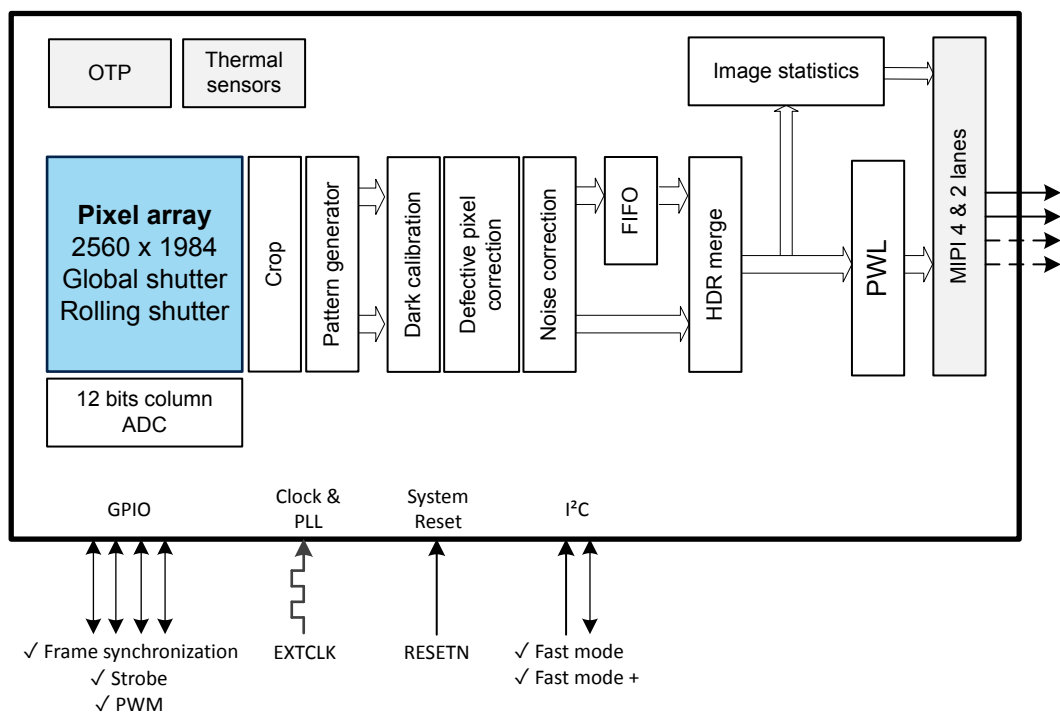
A MIPI line containing image status can be added prior image content (TOP status line), statistics, and histograms can be appended at the end of each image (bottom status line).

The sensor can operate in leader mode (free running) or follower mode based on triggering event on one selected GPIO.

The device is fully configurable through the I²C interface and provides flexible frame-to-frame parameter configuration changes via the use of programmable contexts.

It also embeds a one-time programmable (OTP) nonvolatile memory, structured in 32-bit words that can be used for traceability and customer data.

Figure 1. Functional block diagram

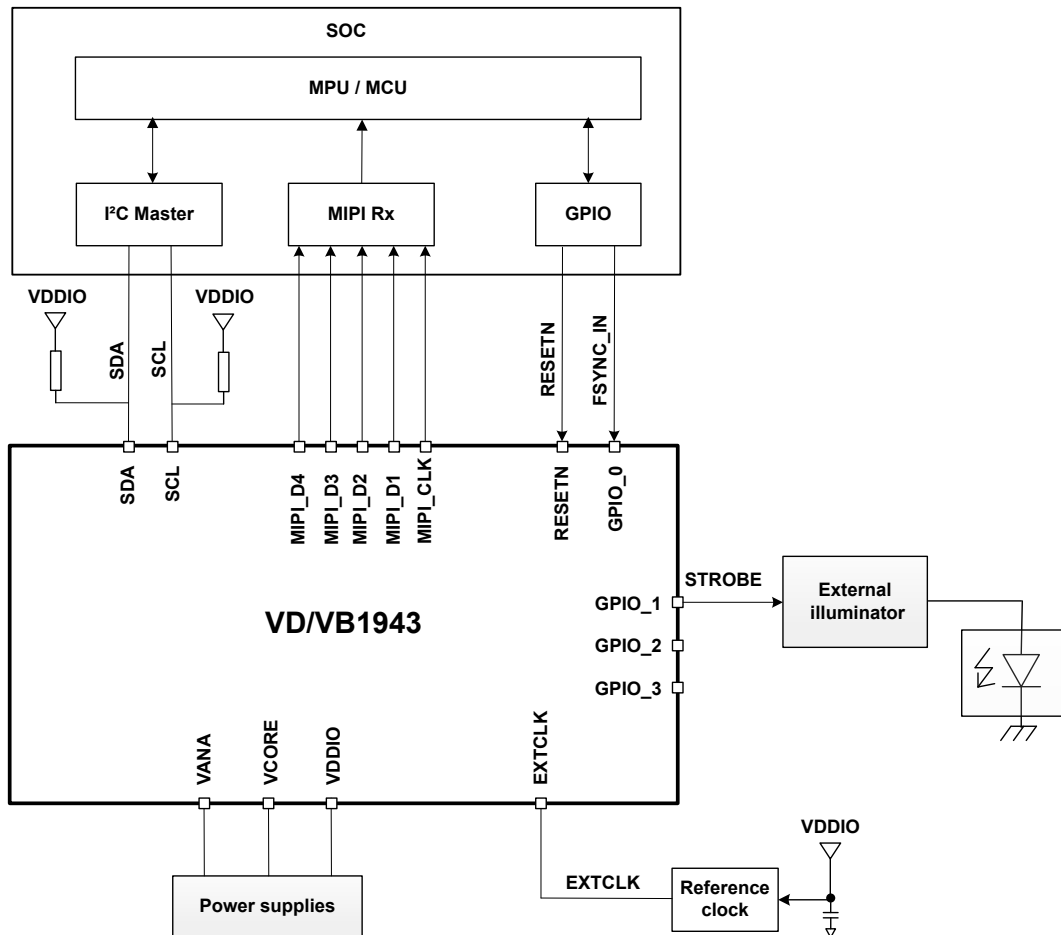


Prerelease product(s)

1.3 Typical configuration into application

The typical device integration is shown in the figure below:

Figure 2. Typical application implementation



On top of interfacing with SoC/MCU, the sensor can support the following features:

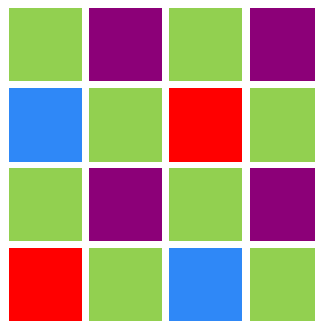
- Synchronization with a second camera module as leader or follower mode.
- Control external illumination system synchronized to exposure period with configurable PWM generation.
- Additional input/output digital control capabilities.

2 Optical characteristics

2.1 Device specific color filter array

When the sensor array is read, the output order of red, green, blue, and NIR depends on the settings of the vertical flip and horizontal mirror. Figure 3. Color filter array shows the readout order of the default settings when the vertical flip and horizontal mirror are both turned off. Refer to the product user manual for a complete description of the different output patterns according to the orientation.

Figure 3. Color filter array



RGB-NIR 4x4

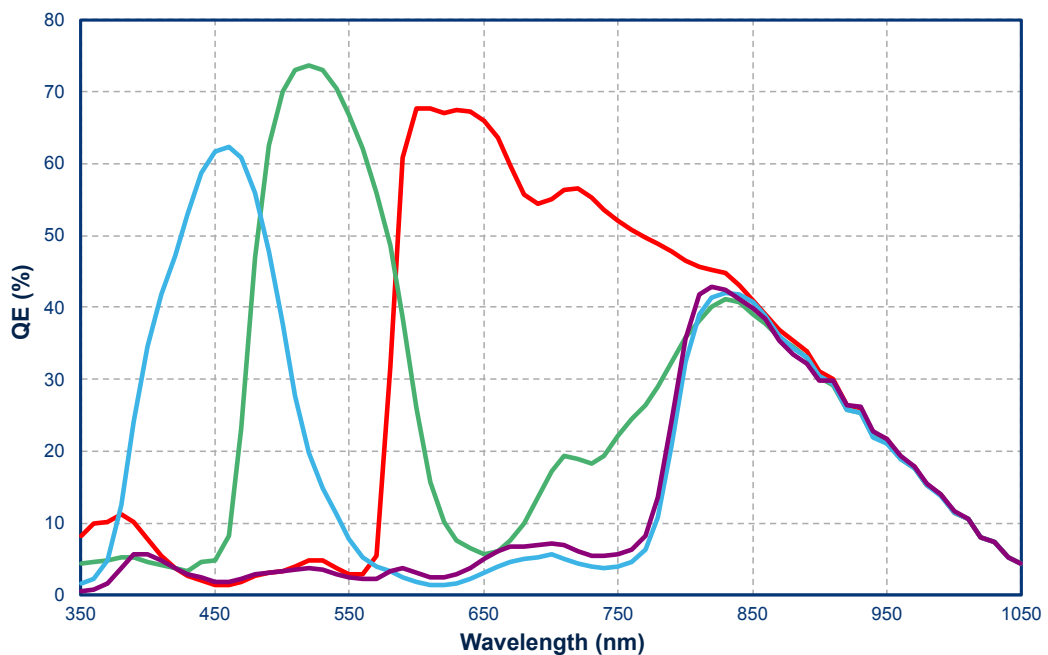
2.2 Optical performance

Typical pixel performance is described in the curves below.

2.2.1 Quantum efficiency

Quantum efficiency (QE) is the percentage of incident photons converted into electrons.

Figure 4. VB1943 peak QE (60°C)



Prerelease product(s)

Figure 5. VD1943 peak QE (60°C)

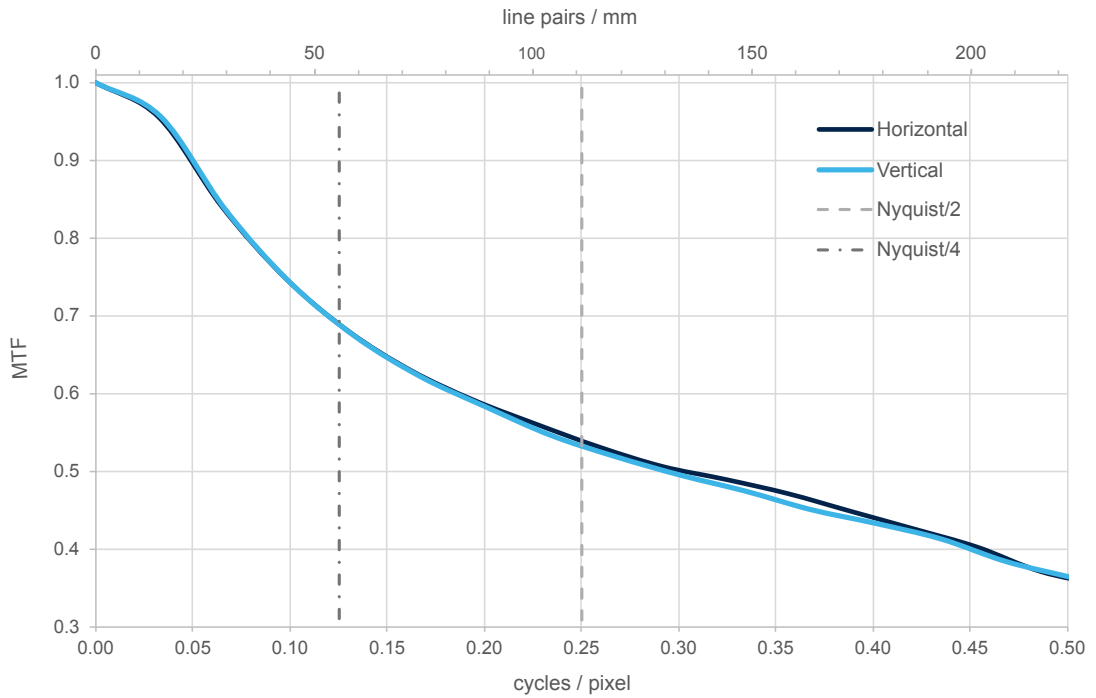


Prerelease product(s)

2.2.2 Modulation transfer function

The modulation transfer function (MTF) measures the ability of the devices to differentiate spatial frequencies. The MTF value represents the contrast restitution for the corresponding spatial frequency. In other words, it describes the contrast attenuation. It is a sharpness indicator that quantifies the extent to which image sensors can capture and discriminate fine detailed contrast of objects within the field of view. The figure below presents the on-axis MTF, measured in a 100x100 pixel ROI using the slanted-edge method, following ISO12233 sfrmat5.

Figure 6. Modulation transfer function (MTF) on axis at 940 nm



Prerelease product(s)

2.2.3 Microlens shift and CRA matching

The VB1943 and VD1943 include an array of microlenses. One microlens being placed on top of each pixel to better focus light on the photosensitive area as a magnifying glass so that incoming light is optimized in the image sensor.

The microlens shift is linear with a maximum of 20° in corners. The table provides the optimal lens chief ray angle (CRA) with regard to distance from the optical center.

With NIR source (940 nm), there is a significant tolerance to lens CRA because the relative illumination remains higher than 90% over the full matrix. This is true even with significant mismatch of lens CRA to microlens shift.

With visible source, there is a general tolerance to the lens CRA, see the figure below. Up to 10° mismatch, the relative illumination loss is much lower than the one from the lens itself (vignetting).

Figure 7. Lens CRA tolerance in visible (green)

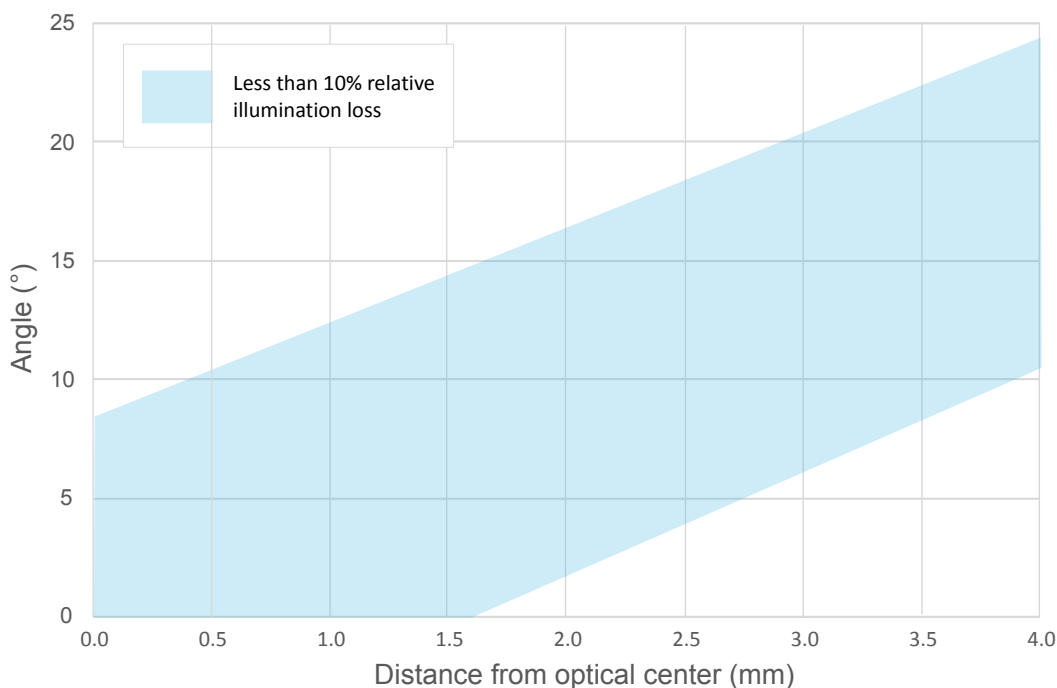


Table 4. Optimal CRA

Distance (mm)	CRA (deg)
0.0	0
0.5	3
1.0	6
1.5	8
2.0	11
2.5	14
3.0	17
3.5	19
3.6	20

3 Product integration

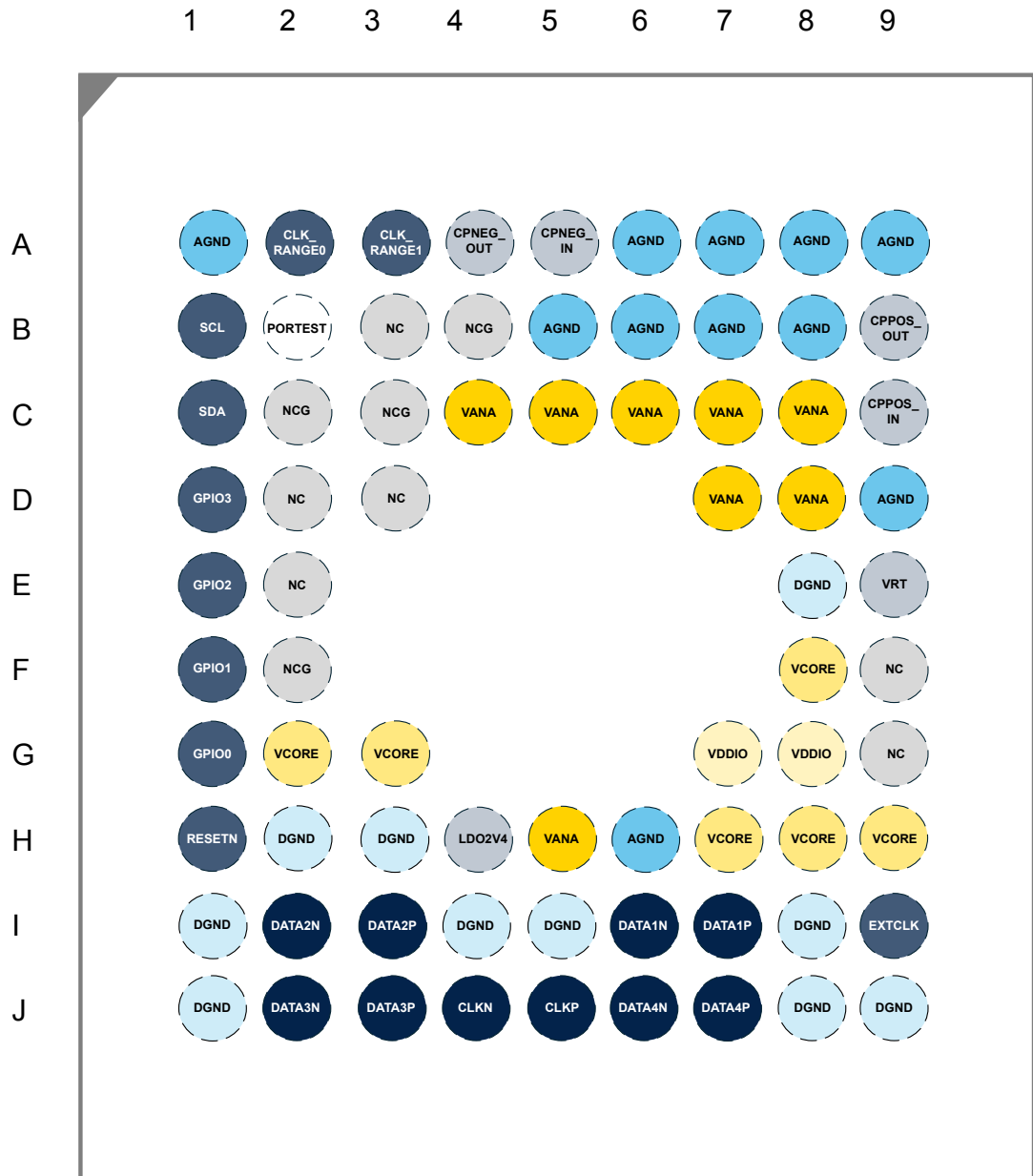
3.1 Device signal descriptions

Table 5. Signal descriptions

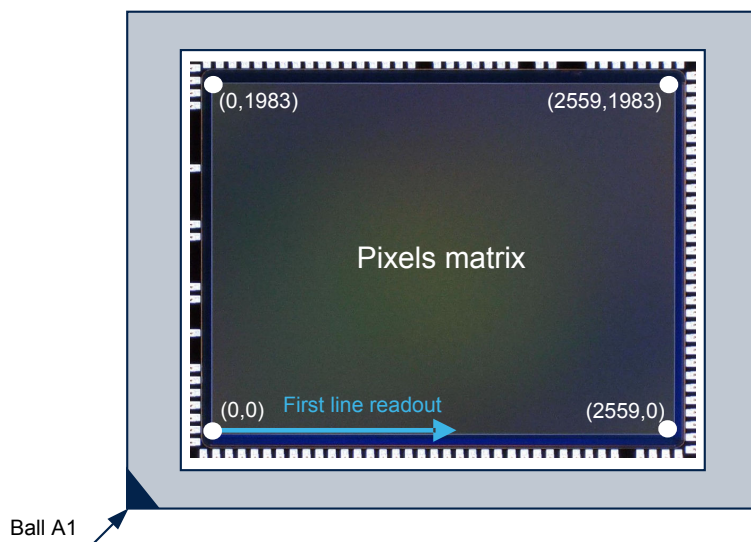
Ball name	Type	Description	Reset state	Reference supply
Power supply				
VANA	PWR	2.8 V power supply for the analog blocks	—	2.8 V
VCORE		1.15 V power supply for the digital core	—	1.15 V
VDDIO		1.8 V power supply for the input/output	—	1.8 V
DGND		Digital ground	—	VDDIO
AGND		Analog ground	—	VANA
Reference				
LDO2V4	REF	Internal reference (must be connected)	—	VANA
CPNEG_IN		Must be connected to CPNEG_OUT	—	VANA
CPNEG_OUT		Must be connected to CPNEG_IN	—	
CPPOS_IN		Must be connected to CPPOS_OUT	—	
CPPOS_OUT		Must be connected to CPPOS_IN	—	
VRT		Internal reference (must be connected)	—	VANA
CSI-2 interface				
DATA1P, DATA1N	MIPI DPHY	CSI-2 data lane 1, positive and negative	Low	VCORE
DATA2P, DATA2N		CSI-2 data lane 2, positive and negative		
DATA3P, DATA3N		CSI-2 data lane 3, positive and negative		
DATA4P, DATA4N		CSI-2 data lane 4, positive and negative		
CLKP, CLKN		CSI-2 clock, positive and negative		
Host interface				
RESETN	I	Reset active low	—	VDDIO
SDA	I/O	I ² C data	—	
SCL	I	I ² C clock	—	
GPIO0	I/O	General purpose I/O and strobe light control (FAIL SAFE pad)	Input	
GPIO1				
GPIO2				
GPIO3				
CLK_RANGE0	I	To select the range of the input clock (FAIL SAFE pad)	—	
CLK_RANGE1	I			
EXTCLK	I	Input clock	—	
Other balls				
PORTEST	I	Must be connected to the digital ground	—	VDDIO
NC	—	Must not be connected and must be left floating	—	—
NCG	I	Can be left floating or connected to analog ground	—	VANA

3.1.1 OBGA package ball assignment

Figure 8. Ball assignment (see-through view)



Prerelease product(s)

Figure 9. Die orientation in OBGA package (top view)

Table 6. Ball assignment table

Ball ID	Signal
A1	AGND
A2	CLK_RANGE0
A3	CLK_RANGE1
A4	CP_NEG_OUT
A5	CP_NEG_IN
A6	AGND
A7	AGND
A8	AGND
A9	AGND
B1	SCL
B2	PORTEST
B3	NC
B4	NCG
B5	AGND
B6	AGND
B7	AGND
B8	AGND
B9	CP_POS_OUT
C1	SDA
C2	NCG
C3	NCG
C4	VANA
C5	VANA
C6	VANA
C7	VANA

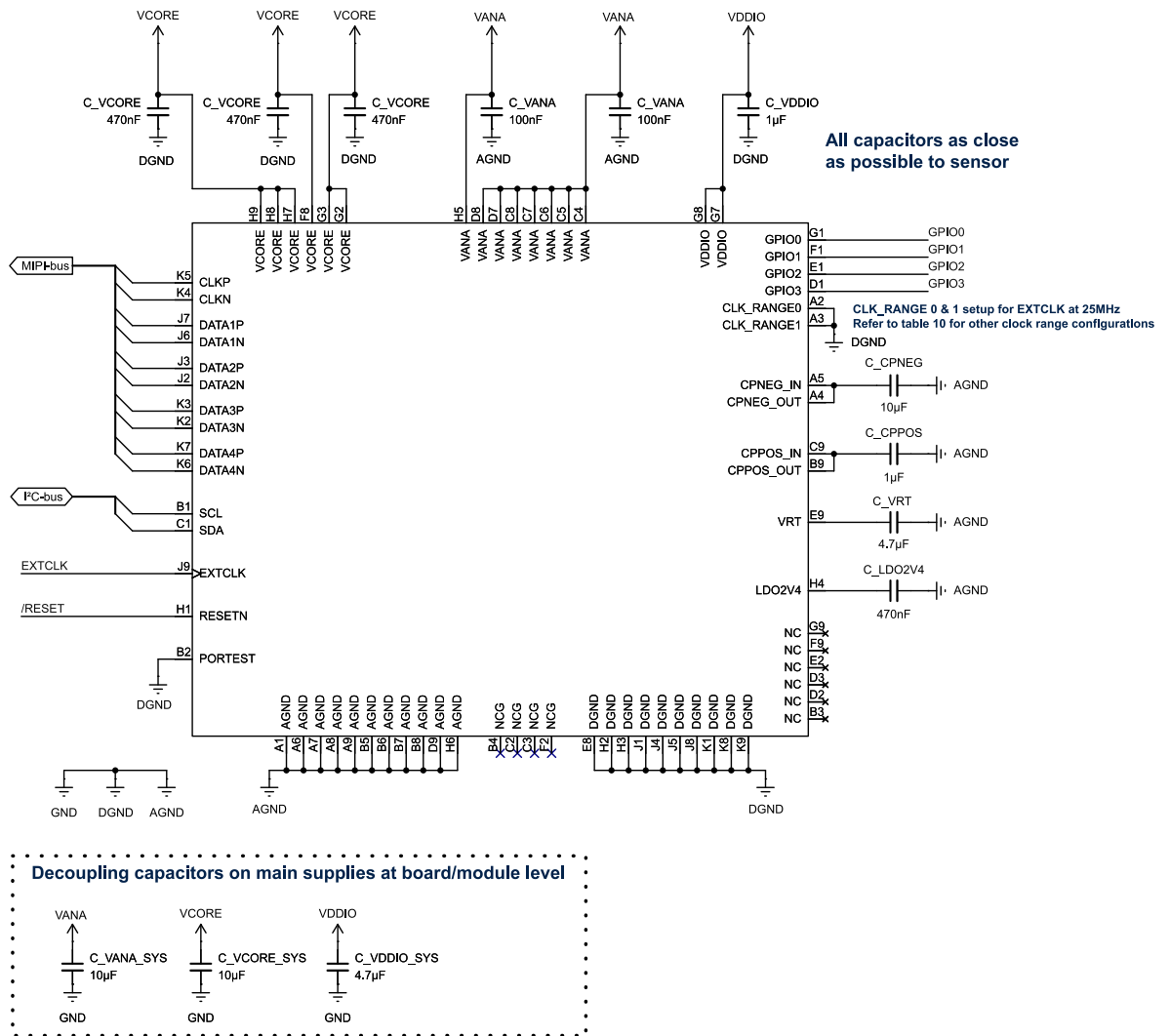
Prerelease product(s)

Ball ID	Signal
C8	VANA
C9	CP_POS_IN
D1	GPIO3
D2	NC
D3	NC
D7	VANA
D8	VANA
D9	AGND
E1	GPIO2
E2	NC
E8	DGND
E9	VRT
F1	GPIO1
F2	NCG
F8	VCORE
F9	NC
G1	GPIO0
G2	VCORE
G3	VCORE
G7	VDDIO
G8	VDDIO
G9	NC
H1	RESETN
H2	DGND
H3	DGND
H4	LDO2V4
H5	VANA
H6	AGND
H7	VCORE
H8	VCORE
H9	VCORE
J1	DGND
J2	DATA2N
J3	DATA2P
J4	DGND
J5	DGND
J6	DATA1N
J7	DATA1P
J8	DGND
J9	EXTCLK
K1	DGND

3.2 Application schematic

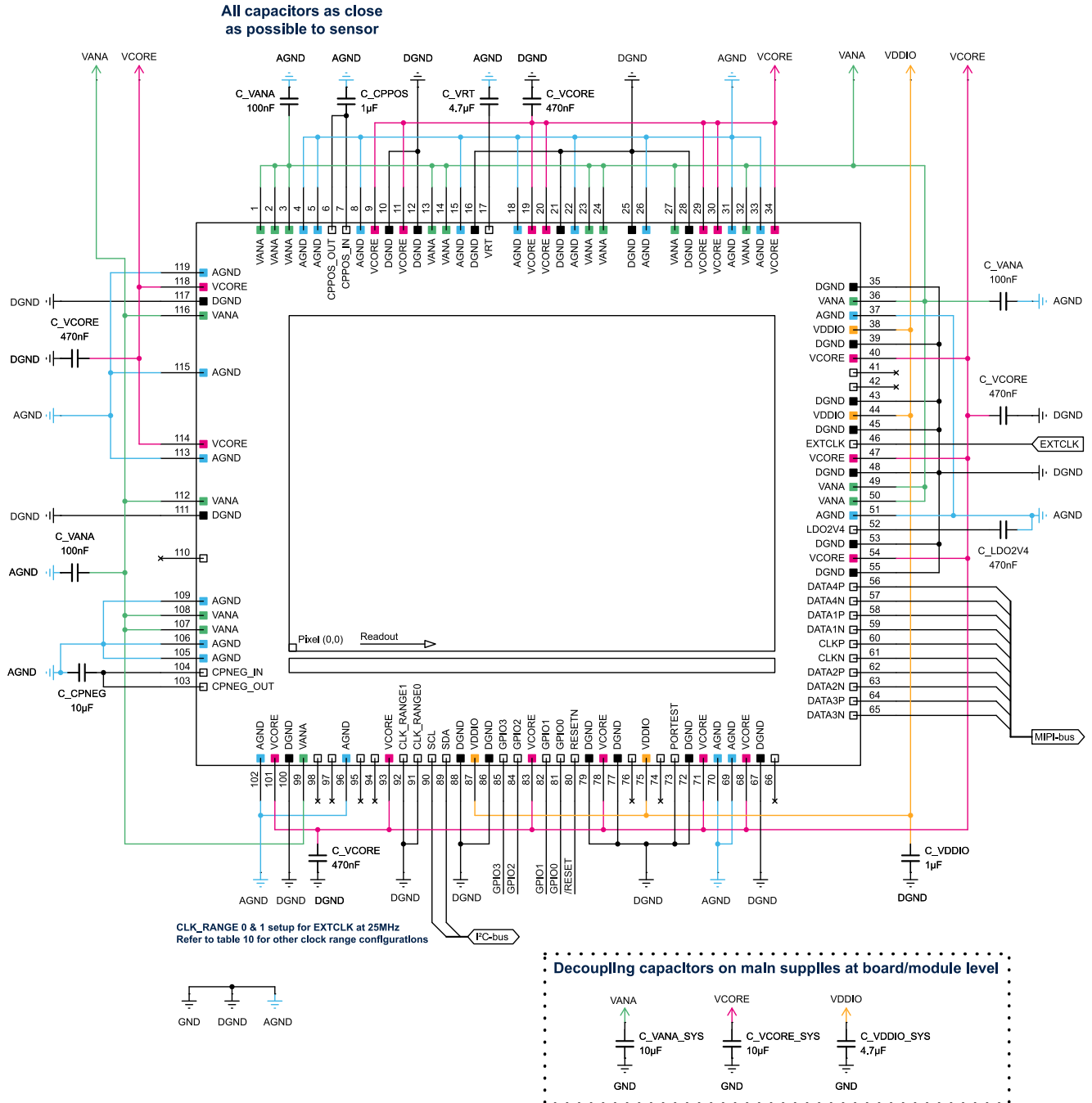
3.2.1 OBGA typical application schematic

Figure 11. OBGA typical application schematic



Prerelease product(s)

3.2.2 Bare die typical application schematic

Figure 12. Bare die typical application schematic


Prerelease product(s)

3.2.3 Additional external components

Dedicated capacitors are required to complete the circuit, especially to filter out supply noise properly. The table below presents the range of the different capacitances. Values are provided after voltage derating only; capacitors should be selected to maintain their capacitance within the range while considering operating conditions (tolerance, aging, temperature).

Large bulk capacitors are recommended to filter low frequency at the entry point of the main power supply on the PCB.

- C_VANA_SYS
- C_VCORE_SYS

Other capacitors shall be placed as close to the pins as possible.

Table 7. Capacitor needs

Name	Associated pin	Voltage	Minimum capacitance	Maximum capacitance	Operating frequencies	Ground	Purpose
C_VANA	VANA	2.8 V	100 nF	—	160 MHz	AGND	Supply decoupling
C_VANA_SYS	VANA	2.8 V	10 μ F	—	160 MHz	AGND	Supply decoupling
C_VCORE	VCORE	1.15 V	470 nF	—	1.0 to 1.5 GHz	DGND	Supply decoupling
C_VCORE_SYS	VCORE	1.15 V	10 μ F	—	160 to 200 MHz	DGND	Supply decoupling
C_VDDIO	VDDIO	1.8 V	1 μ F	—	1 MHz	DGND	Supply decoupling
C_CPPOS	CPPOS_IN, CPPOS_OUT	3.55 V	470 nF	1 μ F	500 MHz	AGND	Bulk capacitor
C_CPNEG	CPNEG_IN, CPNEG_OUT	-2.0 V	4 μ F	12 μ F	500 MHz	AGND	Bulk capacitor
C_LDO2V4	LDO2V4	2.4 V	100 nF	1 μ F	DC	AGND	Bulk capacitor
C_VRT	VRT	2.5 V	2.4 μ F	5 μ F	DC	AGND	Bulk capacitor

3.3 Layout guidelines

In addition to the component selections, their placement and layout play a critical role.

3.3.1 General rules

- Use power and ground planes to supply power to the sensor.
- Join AGND and DGND into one single, solid ground plane underneath the sensor.
- Connect this GND plane to the sensor pins with one via per GND pin when possible.
- Maximize copper fill on the power planes near the sensor and use vias to improve heat transfer from the sensor. Do not place any power dissipative component under or close to the sensor.

3.3.2 Charge pumps (positive and negative)

- Connect CPNEG_IN and CPNEG_OUT with a short track. Place the bulk capacitor C_CPNEG on this path, and not on an isolated track.
- Connect CPPOS_IN and CPPOS_OUT with a short track. Place the bulk capacitor C_CPPOS on this path, and not on an isolated track.

3.3.3 CSI-2 signal traces

- Route the high-speed signal pairs of the MIPI CSI-2 interface with balanced and controlled impedance traces (50 ohms common-mode and 100 Ω differential). This is a requirement for high-speed signaling.
- Route each pair together and match them in length to minimize skew below 10 ps.
- Keep traces on layers adjacent to the ground plane.

3.3.4 Electromagnetic compatibility (EMC)

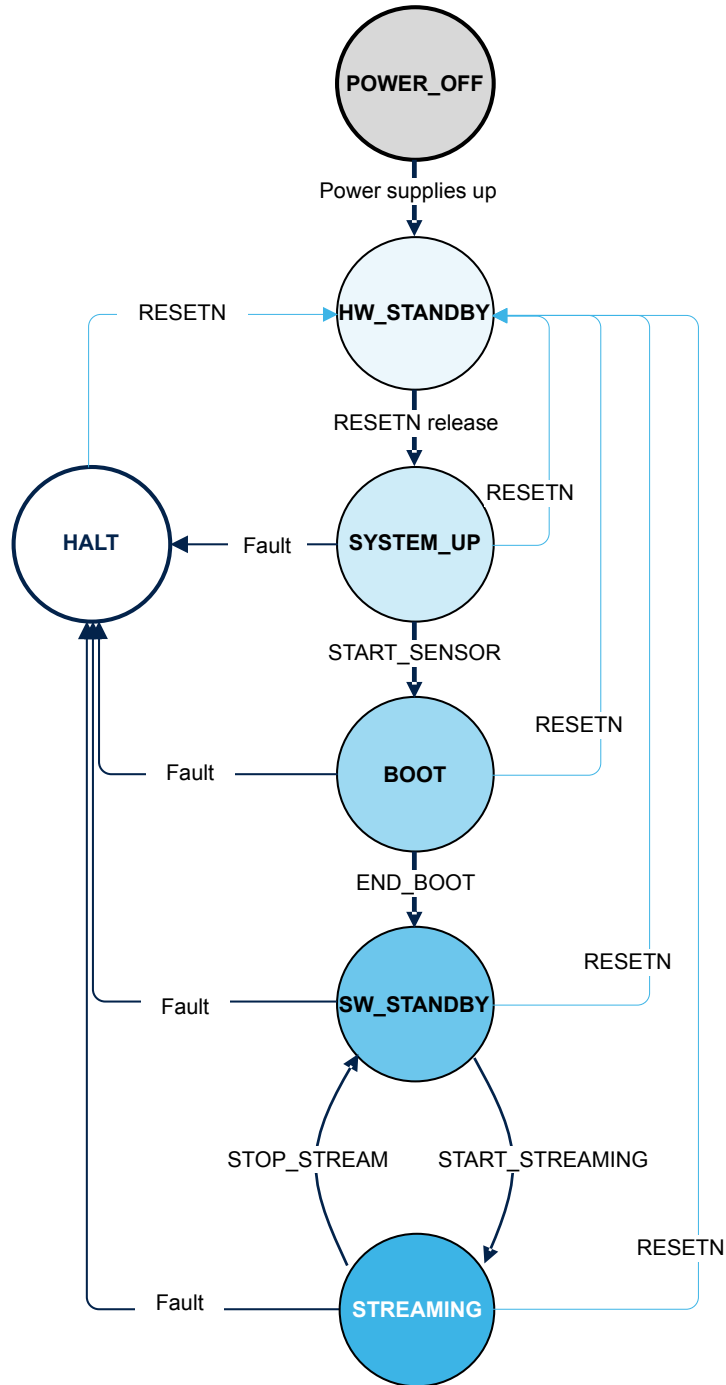
Electromagnetic compatibility (EMC) recommendations are linked to PCB design and routing, below are some guidelines:

- MIPI related recommendations:
 - Use common-mode filters (ECMF) for MIPI data lanes
 - Bury the MIPI tracks (stripline transmission line type)
 - Minimize the skew thanks to equalized length of MIPI lanes track to ensure the same signal propagation time
 - Preserve signal integrity using matched lines having a 50 ohms common-mode impedance and 100 ohms differential impedance.
- Power supplies related recommendations:
 - Use ferrites for parasitic signal filtering
 - Add decoupling capacitors (refer to [Section 3.2.3: Additional external components](#))
 - As close as possible from the power supplies
 - For each power domain, use multiple capacitance values in different ranges to spread the self-ringing frequency
 - Smaller values are fitted closer to the sensor
 - Use a dedicated power supply for the sensor, not shared with other components
- Ground management:
 - Add a ground ring all around the PCB and on all layers. Interconnect the ground planes on the different layers using a multitude of vias
- Limit overshoots on external clock
- Ensure that there is no track close to the PCB border

4 Product features

4.1 Device state machine and state definition

Figure 13. Firmware state machine



Prerelease product(s)

POWER_OFF state

In this state, the power supplies are switched off.

HW_STANDBY state

In this state the device is supplied, EXTCLK must run, and the RESETN pin is asserted LOW. The sensor is ready to start.

SYSTEM_UP state

In system-up state, I²C operations are allowed. Firmware execution is started. The external clock frequency and eventually new I²C address can be configured.

BOOT state

After execution of command START_SENSOR, the sensor transitions to boot state. The internal clocks are initialized, and NVM content is retrieved by the firmware.

SW_STANDBY state

After execution of command END_BOOT, the sensor transitions to software standby state. At that point, I²C instructions are sent by the host to configure MIPI settings, static and dynamic streaming settings.

STREAMING state

After execution of the command STREAMING, the sensor transitions to streaming state and starts transmitting frames over the MIPI interface. In streaming state, only dynamic settings can be changed.

The system status can be read via I²C in UI status registers, or from the MIPI TOP ISL.

HALT state

In HALT state, streaming is interrupted and the sensor goes in a dead-end state, only the cycling RESETN pin can exit the sensor from HALT state.

The I²C is still functional to allow the host to read the UI status registers to assess the error detected.

4.2 Device power up/power down sequence and general control interfacing

4.2.1 Device power up sequence

To power on the device, all external supplies (VANA, VCORE, VDDIO) must be properly provided according to the device characteristics described in [Section 7: Electrical characteristics](#). As long as RESETN is low, the device is in HW_STANDBY state.

The power on sequence must be done as follows:

1. Provide all the external supplies (VANA, VCORE, VDDIO) according to the device characteristics described in [Section 7: Electrical characteristics](#). As long as RESETN is low, the device is in HW_STANDBY state.
2. External supplies can be switched on in any order, as well as EXTCLK.
3. Set RESETN to high.

Figure 14. Device power up to streaming mode sequence

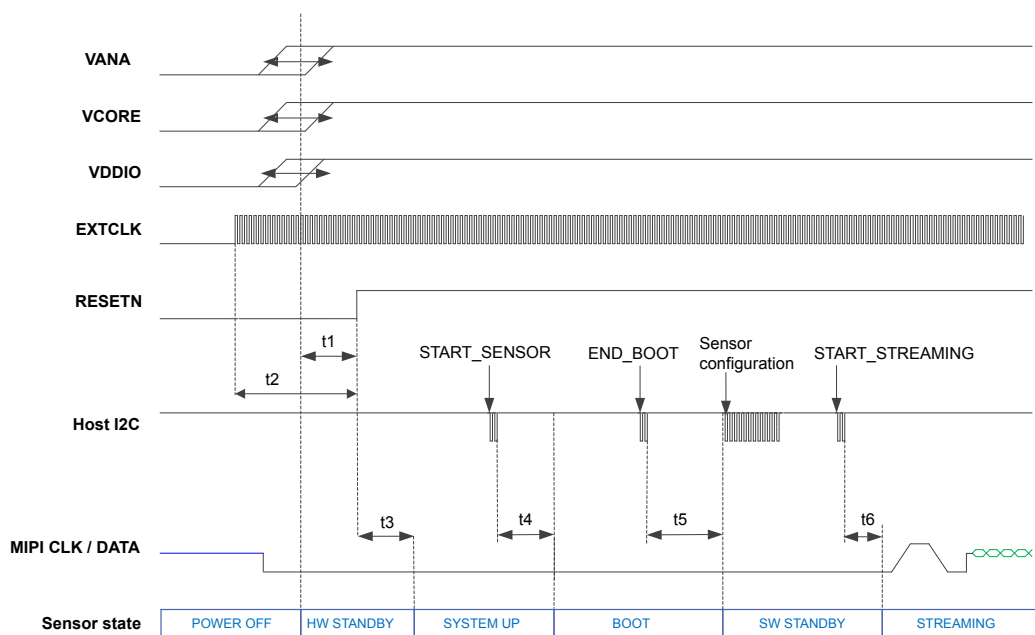


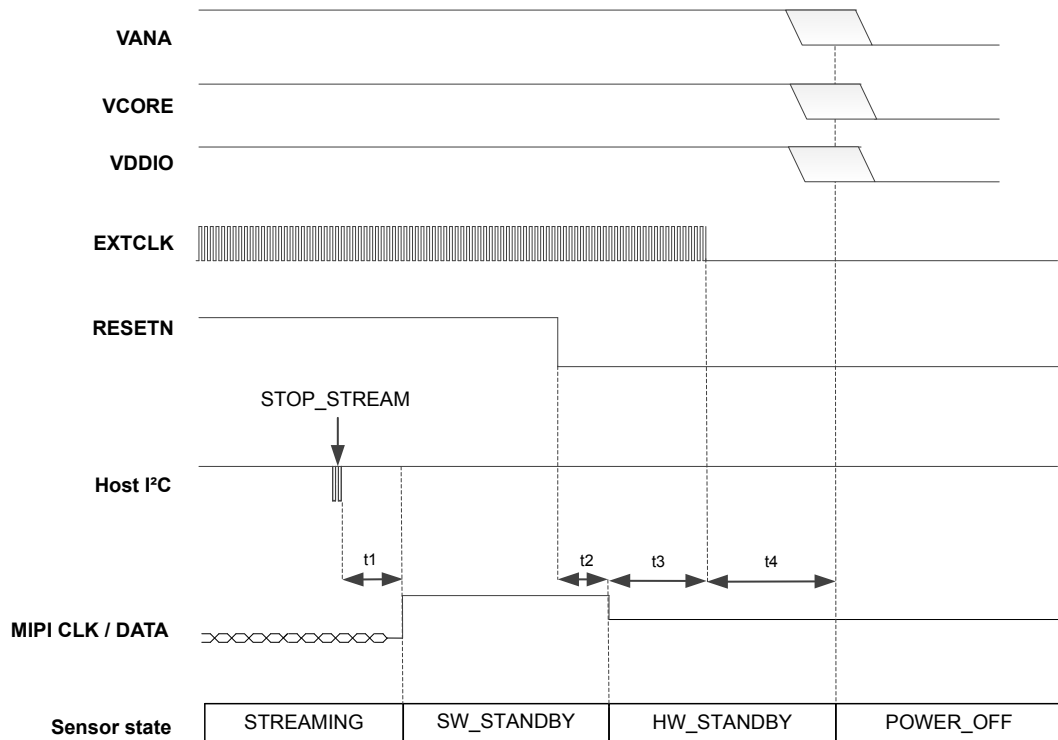
Table 8. Power up sequence timings

Timing	Description	Typical delay (EXTCLK= 25MHz, I2C 1MHz)
t1	POWER SUPPLIES stable to RESETN signal released	100us
t2	CLOCK stable to RESETN signal released	1us
t3	RESETN signal released to SYSTEM_UP state	5.5ms
t4	START_SENSOR command to BOOT state	1.8ms
t5	END_BOOT command to SW_STANDBY state	4ms
t6	START_STREAMING command to STREAMING state	4ms

4.2.2 Device power down sequence

The power down sequence must be done as follows:

1. Send the command to stop the streaming and wait until sensor reaches SW_STANDBY state.
2. Release RESETN pin (low level).
3. Shutdown EXTCLK.
4. External supplies can be switched off in any order.

Figure 15. Power down sequence

Table 9. Power down sequence timings

Timing	Description	Typical delay (EXTCLK = 25 MHz)
t1	STOP_STREAM command to SW_STANDBY state	Less than two frames periods
t2	RESETN signal assertion HW_STANDBY state	Simultaneous
t3	HW_STANDBY state to EXTCLK stopped	Any
t4	EXTCLK stopped to POWER SUPPLIES down	Any

4.2.3 Power supplies

Three power supplies required by the sensor are:

- 2.8 V for the analog blocks
- 1.15 V for the core digital logic and MIPI CSI-2 output driver
- 1.8 V for the digital I/Os

The pixel array requires different positive and negative voltages, all internally generated by charge pumps and regulators. Four voltage references, internally generated, need external decoupling capacitors. The internal CPU handles the entire power management of the sensor to ensure the lowest power consumption at any given time.

The sensor's internal CPU handles the entire power management to ensure the lowest power consumption.

Internal voltage reference supplies are powered up as soon as a streaming command is issued.

4.2.4 Clock and phase-locked loop (PLL)

An input clock is required from an external digital clock source in the range of 12 MHz to 50 MHz. Firmware is preconfigured for a 25 MHz external source clock. Two built-in, phase-locked loop (PLL) blocks generate all necessary internal clocks for the pixel array, processing pipe, embedded CPU, and output interface.

The internal CPU handles the PLL startup/down sequence when the device is entering/stopping the streaming mode to ensure the lowest power consumption.

4.2.4.1 Input clock configuration

Because the input clock (EXTCLK) supports a wide range of frequencies (12 MHz to 50 MHz), it is mandatory to select a sub-range by configuring two inputs of the device: CLK_RANGE0 and CLK_RANGE1.

Moreover, there is a value for each configuration to specifically optimize the boot time of the sensor. Refer to the table below:

Table 10. Input clock configuration

CLK_RANGE0	CLK_RANGE1	Range of the input clock	Optimal input clock
Low	Low	25 MHz (default value)	25 MHz
High	Low	12 – 24 MHz	24 MHz
Low	High	24.01 – 36 MHz	36 MHz
High	High	36.01 – 50 MHz	50 MHz

The reference supply of these inputs is VDDIO.

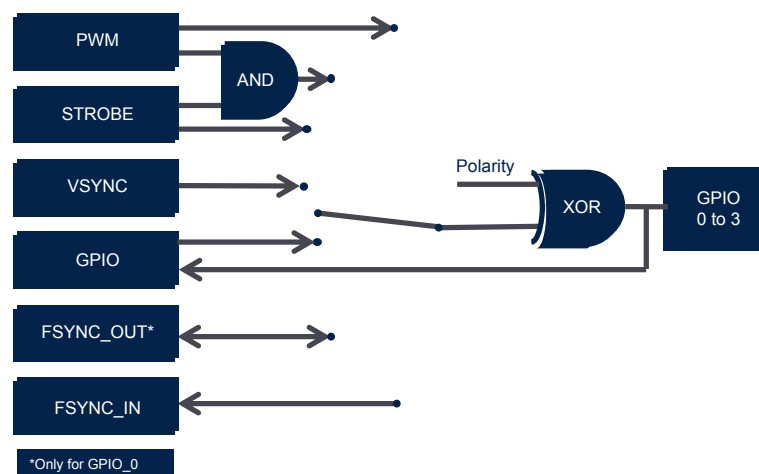
4.2.5 General-purpose control pin behavior

The sensor provides four GPIOs with different modes:

- Frame start synchronization
- Strobe output
- PWM output
- Strobe PWM output
- Generic GPIO

All GPIOs have configurable polarity (see figure below).

Figure 16. GPIO section modes



GPIOs can also be configured to input state.

The typical pull-down value is 50 KΩ.

The below table provides the behavior of the different GPIOs according to the sensor state.

Table 11. GPIO behavior for the different FSM states

GPIO	HW_STANDBY		SYSTEM_UP/BOOT		SW_STANDBY		STREAMING GP_in or DISABLED mode	
	I/O direction	Mode	I/O direction	Mode	I/O direction	Mode	I/O direction	Mode
GPIO_0	INPUT	Pull down	OUT	Drive low	INPUT	Pull down	INPUT	Pull down
GPIO_1	INPUT	HiZ	OUT	Drive low	INPUT	Pull down	INPUT	Pull down
GPIO_2	INPUT	HiZ	OUT	Drive low	INPUT	Pull down	INPUT	Pull down
GPIO_3	INPUT	HiZ	INPUT	Pull down	INPUT	Pull down	INPUT	Pull down
CLK_RANGE0	INPUT	Pull down	INPUT	Pull down	INPUT	Pull down	INPUT	Pull down
CLK_RANGE1	INPUT	Pull down	INPUT	Pull down	INPUT	Pull down	INPUT	Pull down

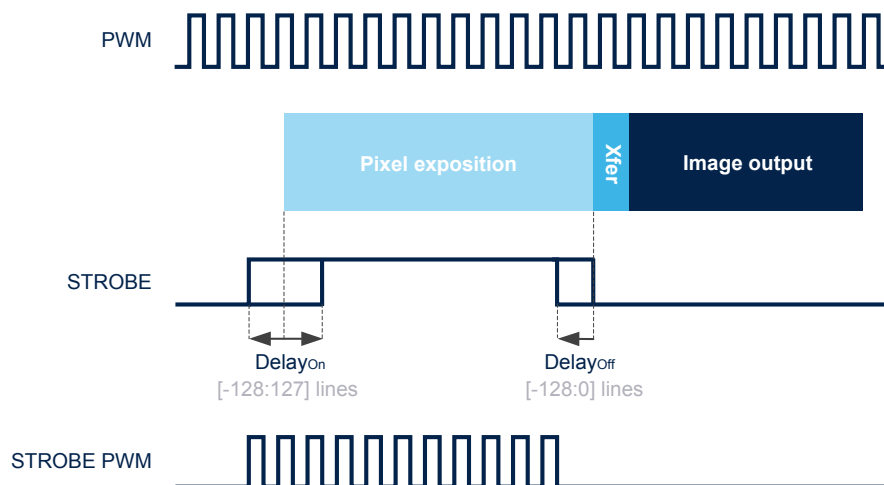
4.2.5.1 Device synchronization modes

The sensor has two synchronization modes:

1. Leader: In this mode, the device controls the internal frame sequencing and can synchronize other follower sensors with the FSYNC_OUT signal (only available on GPIO0).
2. Follower: In this mode, the internal sequencer starts the pixel exposure when receiving the synchronization signal rising edge FRAME_START. A programmable delay can be added between the synchronization signal and the start of integration.

4.2.5.2 Device peripheral synchronization and PWM capability

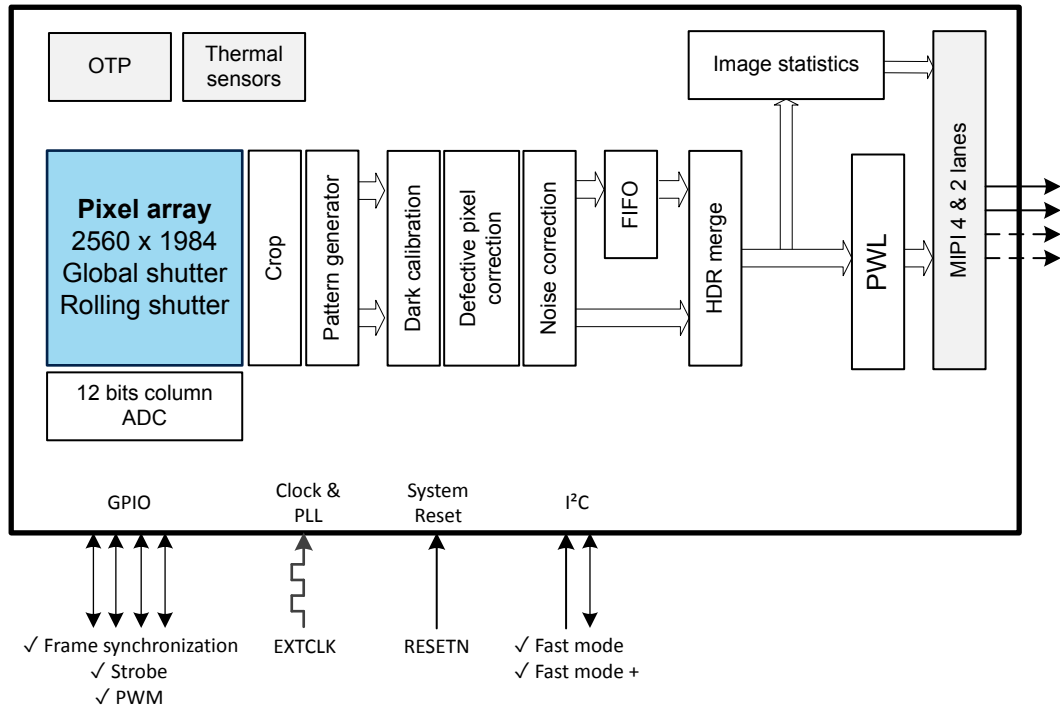
In both synchronization modes, the device can generate on GPIOs PWM or STROBE PWM signals. It can be used for driving an illumination system or other. The STROBE signal available on any GPIO is synchronized with the sensor integration period as shown in the figure below.

Figure 17. Pulse-width modulation (PWM) and STROBE overview


Prerelease product(s)

4.3 Image processing features

Figure 18. Functional block diagram



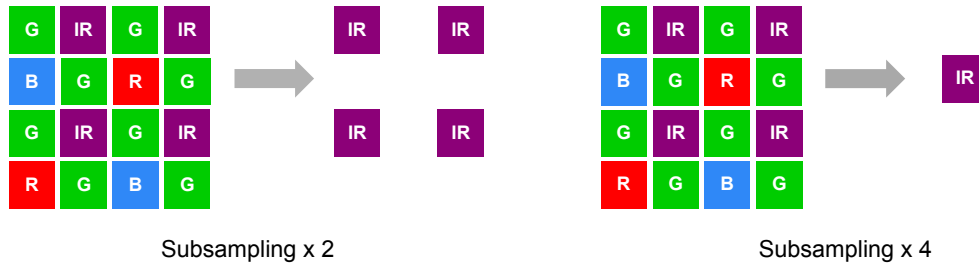
The video pipe performs several features designed to ensure high image quality. These features include:

- Analog subsampling (NIR pixel only)
- Analog gain
- Digital gain
- Pedestal insertion
- Exposure and split exposure control
- Global shutter / rolling shutter
- Test pattern generation
- Automatic dark calibration (linked to temperature)
- Dynamic defective pixel correction
- Dynamic gaussian noise reduction
- Image crop
- Image flip and mirror
- RGB NIR to Bayer RGB conversion
- RGB NIR to mono NIR conversion
- HDR merge (rolling shutter only)
- PWL compression
- Output interface
- Embedded status lines
- Exposure statistics
- Exposure histograms
- Contexts management

4.3.1 Analog subsampling

The device supports x2, x4, and x32 subsampling for NIR pixels, which reduces overall image size and keeps the same FoV. Subsampling is applied vertically and horizontally.

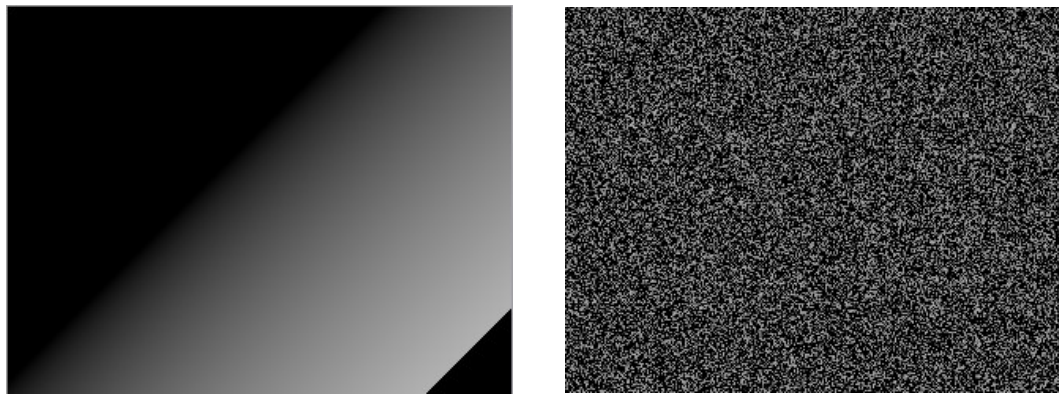
Prerelease product(s)

Figure 19. Subsampling example


4.3.2 Test pattern generation

The pattern generator allows the generation of digital patterns in the output frame. Available patterns are:

- Diagonal grayscale
- Pseudo-random data PN28

Figure 20. Available patterns


Diagonal grayscale

Pseudo-random data

4.3.3 Dynamic defective pixel correction

Active pixels are automatically corrected by a dynamic algorithm embedded in the sensor ISP. This mechanism can be deactivated for debugging purposes and for specific use cases such as structured light.

Small particles on the image matrix array, pixels with upper or lower sensitivity than neighbors, and leaky pixels among the millions of pixels of the matrix appear as unusual spots, being either too dark or too bright.

The embedded automatic defective pixel correction removes defects by performing on-the-fly correction of single or paired defective pixels.

Hence, defect-free images are provided directly from the sensor without requiring further postprocessing at the application level.

The feature performs as follows:

1. For a defined pixel P, the algorithm identifies if there are spatial gradients in the area by considering the values of the surrounding pixels in the same color plane.
2. The algorithm computes the theoretical value V_{theory} that pixel P would have if it was following the spatial gradients identified in the area.
3. The actual value V_{actual} of pixel P is compared to the theoretical value V_{theory} .
4. If V_{actual} is too far from V_{theory} , considering a certain range of tolerance, the pixel P is considered as defective because of its unusual value, and the value of pixel P is replaced by V_{theory} .

Tunable tolerance thresholds allow a perfect balance between systematic defect correction and preserving textures/patterns in the image for various use cases.

Defective pixel correction operates on all the color planes of the RGB-NIR image.

4.3.4 Automatic dark calibration

A dark calibration is performed by extracting the dark rows from the stream, then averaging and removing the dark noise from pixels in the active image.

The pixel matrix has dedicated lines with shielded pixels that are used as references to estimate and subtract dynamically the dark level from the active image. This keeps the dark level constant regardless of the temperature, exposure time, or analog gain changes.

Temporal smoothing and fractional bit dithering are applied to avoid a sudden one-code step.

This block also embeds a programmable digital gain control feature, independent for each channel (R,G,B,NIR) with a granularity of 1/256 code.

And last, a configurable pedestal can offset the dark level along the ISP pipe.

4.3.5 Cropping

The image dimension can be horizontally and vertically reduced to a smaller region of interest (ROI) with adjustable position in the active matrix.

Cropping is allowed in X and Y direction independently, ROI width and height must be a multiple of 4 pixels.

The benefits of cropping the image are:

- Lightening image-processing requirements with less data to process reducing sensor power consumption.
- Increasing frame rate by saving both on readout time and preprocessing time.

This increases the frame rate as shown in the table below:

Table 12. Maximum frame rate with reduced image size

Resolution	MIPI 4 lanes		MIPI 2 lanes	
	GS	RS	GS	RS
320 x 240	610	370	590	360
640 x 480	360	200	360	200
1280 x 720	260	140	260	140
1920 x 1080	180	97	129	98

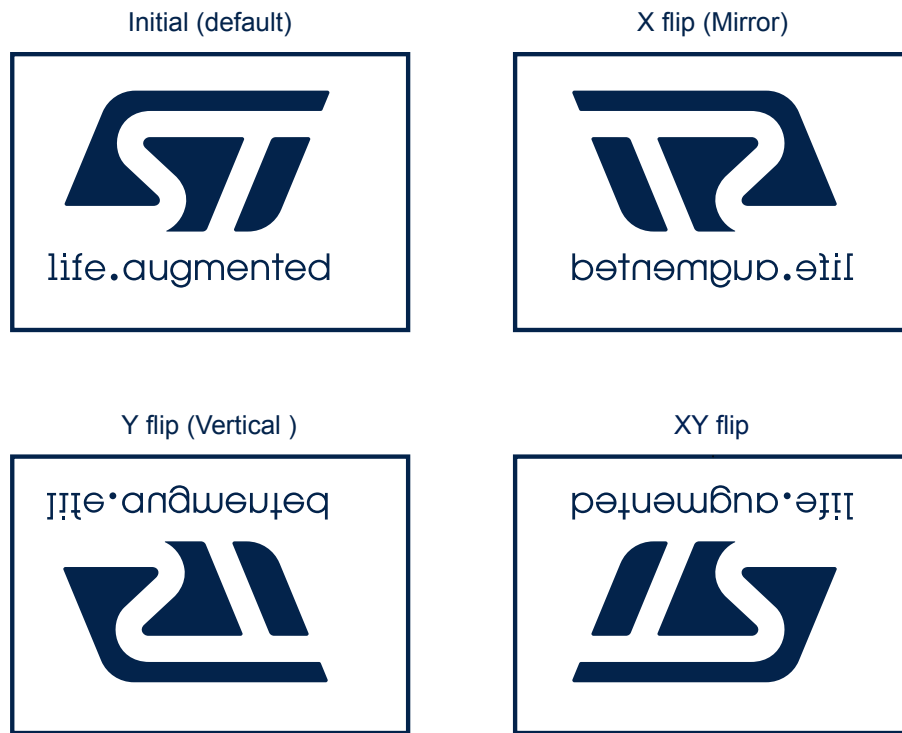
4.3.6 Vertical and horizontal flip

Mirror (or X FLIP) reverses the output image horizontally.

Flip (or Y FLIP) reverses the output image vertically.

Combining both flip and mirror (XY FLIP) rotates the output image by 180°.

Figure 21. Illustration of mirror and flip modes



4.3.7

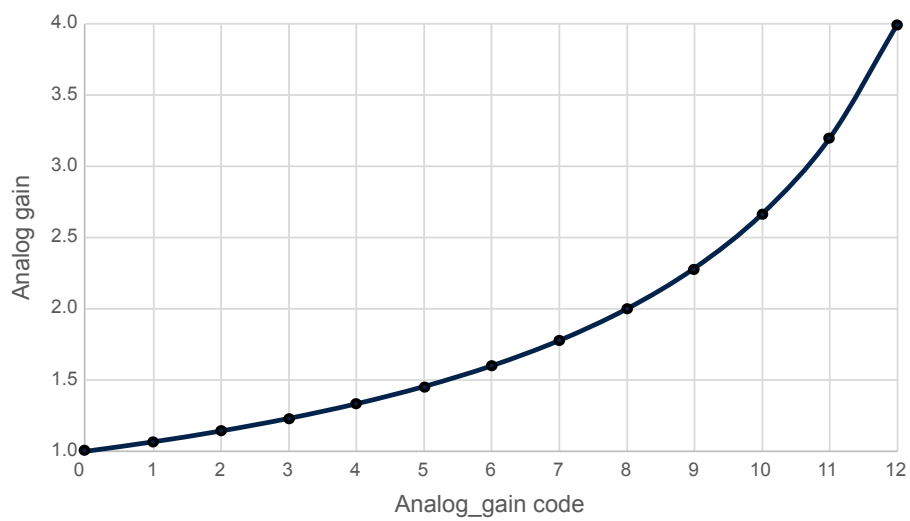
Analog and digital gains

The sensor enables setting analog and digital gains for the capture of clear high-contrast images even in low-light conditions.

Analog gain is common to all pixel types (R,G,B,NIR), while digital gain has a per color plane control.

Analog gain is applied prior to ADC conversion and avoids adding extra noise amplification. Its range is from 1.0 to 4.0 in 12 steps. If required, analog gain must be increased before digital gain.

Figure 22. Analog gain factors available



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Table 13. Available analog gain factors

Analog gain code	Analog gain value
0	1.00
1	1.07
2	1.14
3	1.23
4	1.33
5	1.45
6	1.60
7	1.78
8	2.00
9	2.29
10	2.67
11	3.20
12	4.00

Digital gain is applied inside ISP digital pipe after dark calibration stage. Its range is from 0 to 32 with a 1/256th step.

4.3.8 PWL compression

Piecewise linear (PWL) compression involves applying a compression or decompression function to the incoming pixel stream. It maps the input dynamic range to the output range according to a programmable piecewise linear transformation function. The curve of the function must be monotonic and is described using 32 points as free (X, Y) doublets that give a high level of flexibility in curve shapes and accuracy.

PWL compression may be used to decrease the required bit width RAW resolution. This is achieved by applying a compression curve which reduces the overall dynamic in a nonlinear way.

Pixel resolution at the output of the video pipe is 10 bits (global shutter), 12 bits (rolling shutter SDR), and 18 bits (rolling shutter HDR), while formatting at the output interface is in the range RAW8 to RAW12.

The sensor has four default PWL curves:

- 10 bits to 8 bits (dedicated to global shutter)
- 12 bits to 8 bits (dedicated to rolling shutter SDR)
- 12 bits to 10 bits (dedicated to rolling shutter SDR)
- 18 bits to 12 bits (dedicated to rolling shutter HDR)
- 18 bits to 10 bits (dedicated to rolling shutter HDR)

PWL compression can be reprogrammed by the host to apply custom compression curve when sensor operation is rolling shutter HDR.

4.3.9 Output interface

The OIF embeds quad data lanes to communicate with the MIPI D-PHY interface. It supports up to 1.5 Gb/s of data per lane and can be scaled down to a dual data lanes system. The OIF outputs active pixel data in RAW12, RAW10, or in RAW8. The output interface supports virtual channels and data types.

MIPI lanes polarity and lanes ordering can be reconfigured before starting the image stream.

Table 14. Video mode support

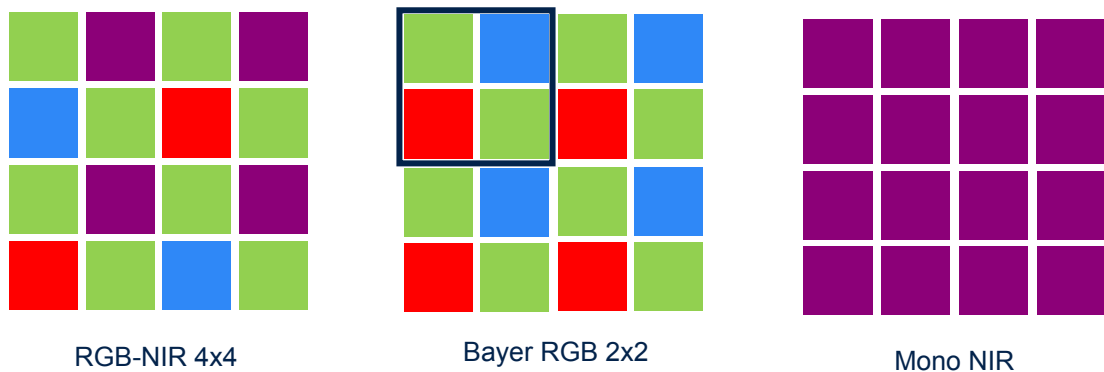
Exposure			MIPI supported format		
Mode	Image output type	Remark	RAW12	RAW10	RAW8
Global shutter	RGB-NIR	Kernel 4x4	—	Direct	PWL 10 => 8
	RGB	Depolluted NIR	—	Direct	PWL 10 => 8
	NIR	With smart upscale	—	Direct	PWL 10 => 8
	NIR subsampled	x2, x4, or x32	—	Direct	PWL 10 => 8
Rolling shutter	RGB-NIR	SDR	Direct	PWL 12 => 10	PWL 12 => 8
	RGB	SDR depolluted NIR	Direct	PWL 12 => 10	PWL 12 => 8
	RGB-NIR	HDR	PWL 18 => 12	PWL 18 => 10	—
	RGB	HDR depolluted NIR	PWL 18 => 12	PWL 18 => 10	—

4.3.10 Device output pattern configuration capabilities

Thanks to its dedicated color filter and internal processing, the sensor can output three different patterns, depending on the selected configuration, as shown in [Figure 23. Output patterns](#).

In addition to standard single-pattern streaming, it is also possible to dynamically combine multiple patterns by chaining several configurations (see [Section 4.3.12: Contexts management](#)).

Figure 23. Output patterns



This Figure illustrates the readout order for the default configuration when both vertical flip and horizontal mirror are disabled.

For a complete description of the available output patterns and their behavior with different image orientations, refer to the product user manual.

4.3.11 Embedded status lines

The output interface (OIF) embeds the intelligent status line (ISL) generator to allow metadata to be sent inside every frame through the MIPI CSI ahead of the image content.

The CPU has access to a bank of status registers, refreshed at each frame, and providing detailed information on the current state of the sensor. Most of the content of this bank is also available in ISLs. The ISLs contain all information related to the current transmitted frame such as:

- Clock settings
- Image cropping and orientation parameters
- Analog and digital gains
- Integration time
- Frame counter index
- Thermal sensor values
- Dark calibration parameters

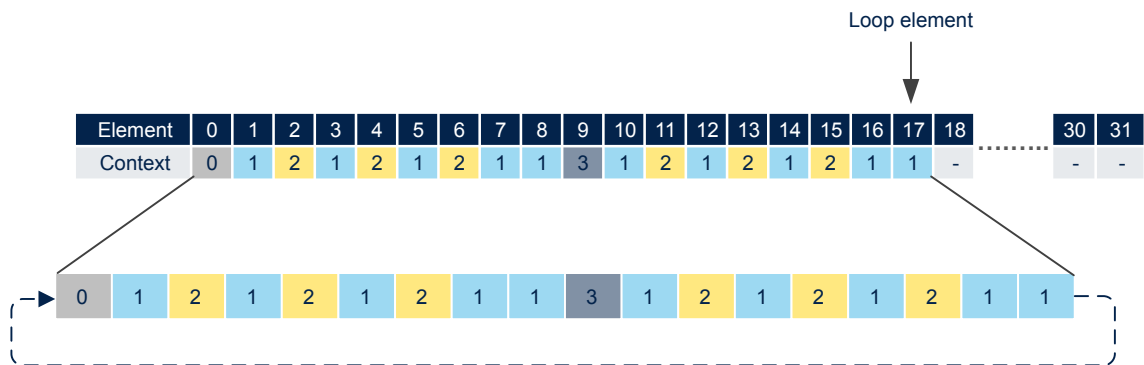
Transmission of ISL data packets can be disabled by configuring a static register during SW STANDBY state before streaming.

4.3.12 Contexts management

The sensor allows the configuration of up to four different contexts (or frame setups).

The context sequence is configured with the context sequencing vector and the loop element register. The context sequencing vector contains 32 2-bit elements. Each element is to select contexts 0, 1, 2 or 3. The loop element register is a value from 0 to 31. Each element from 0 to *Loop element* is executed once and after execution, the next context to be executed is the one defined in *Element 0* (refer to Figure 24. Context sequencing configuration).

Figure 24. Context sequencing configuration



Some context parameters must be defined and stay frozen during streaming (static parameters), while other context parameters such as gain or integration time can be changed while streaming (dynamic parameters).

The sensor can be configured to generate a predefined number of frames before switching automatically back to SOFTWARE_STANDBY without any host supervision. This feature is possible in both leader and follower mode. Context parameters that can be configured through the context management feature are listed in the following table:

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Table 15. Context parameters configurable for sequencing

Parameter	Description
Sensor configuration	Operating mode global or rolling (SDR or HDR) shutter, output pattern and bitwise
Virtual channel	Selection of MIPI virtual channel ID
Frame length	To define the frame rate of the sensor
Image ROI selection	select ROI among four programmable ROIs
Statistics ROI	Define ROI geometry for statistics and histograms computation
GPIOs control	Selectively enable or disable GPIOs features in the context
Defective pixel correction	Enable/disable pixel defect correction and control correction strength
Noise reduction	Enable/disable noise reduction and control reduction strength
DARK pedestal	Enable/disable DARK calibration and set pedestal value
Analog gain	Gain applied before ADC readout to adjust brightness
Digital gain	Gain applied after ADC readout to adjust brightness
Integration time	Adjust the exposure times applied to each frame

4.3.13 Output format and structure of frames

The MIPI frame is made of a succession of long packets.

Each packet is sized to contain the payload of one line whatever the image pixel format.

When enabled, top status line (TOP ISL) is transmitted after the *Start of Frame* short packet. This packet contains the 512 first bytes of the User Interface (UI) status registers, it describes the characteristics of the current image and is refreshed every frame.

TOP ISL packet is padded to have a total length fitting the size of a line packet. If a line packet is below 512 bytes, a second TOP ISL packet is generated.

When enabled, bottom status lines (BOT ISL) are transmitted before the *End of Frame* short packet and contains statistics and histograms of the current frame.

The first packet has an initial padding of 256 bytes. The total number of BOT ISL lines differs according to the number of histograms to output.

BOT ISL packets are padded to have a total length fitting the size of a line packet.

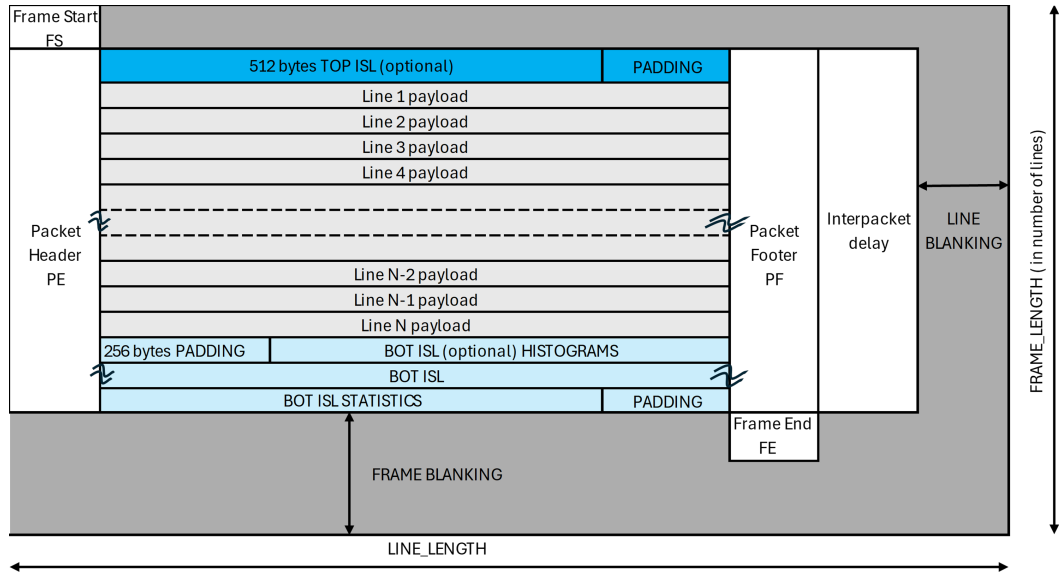
A partial frame buffer allows a MIPI line packet transmission time to be longer than the line period, ie no more line blanking.

Conversely, MIPI line packets may not be transmitted continuously lines after lines, the sensor can insert lines pauses in the MIPI transmission.

The sensor is applying a programmable minimum interpacket delay between line packets.

Images for each of the four contexts have their own configurable virtual channels and datatypes. Top and bottom status lines also have a common configurable datatype.

Figure 25. MIPI frame format



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5 Product interfaces

5.1 Inter-integrated circuit

The image sensor is configured and controlled via an I²C interface operating either in fast mode (400 kHz) or in fast mode plus (1 MHz) at 1.8 V. After the sensor boot sequence, the default I²C configuration is fast mode plus with a sink capability set to 20 mA. Drive capability can be decreased to 4 mA (fast mode) by setting a dedicated register once the system has booted.

Device addressing uses a camera control interface (CCI) protocol with 2-byte subaddresses.

The default sensor address is 0x20 (including R/W bits) and can be overridden permanently (by storing a nonnull value in a dedicated OTP register), or temporarily (by storing a nonnull value in a dedicated user interface register).

5.1.1 Known limitation and workaround

The sensor's I²C interface does not support single or sequential reads that start from the current location. Consequently, you must use a repeated start condition to read the registers.

Figure 26. Incompatible I²C read sequence

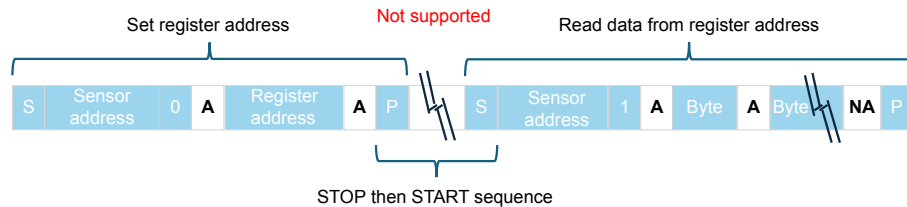
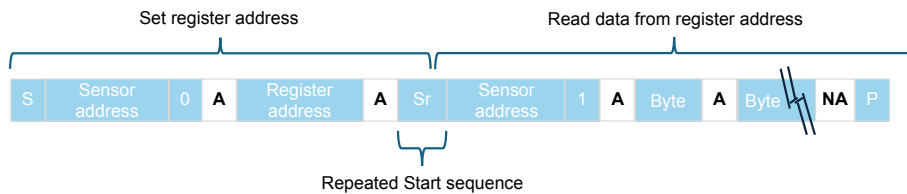


Figure 27. Reliable I²C read sequence



5.2 MIPI CSI-2 interface

The sensor is ready to connect via a quad-lane MIPI CSI-2 serial interface. It is also able to operate on a reduced dual-lane interface. The MIPI CSI-2 serial interface supports up to 1.5 Gbps per lane. It is the industry standard for low electromagnetic interference (EMI) and excellent electromagnetic compatibility (EMC) high-speed interfacing. Resolution is scalable between RAW8, RAW10, and RAW12.

The quad per lane interface does not support an ultralow power state. The clock and data lanes remain in LP-11 (TX-stop state) when the video stream stops.

The interface supports data rates from 300 Mbps up to 1.5 Gbps per lane. However, the minimum data rate for the rolling shutter HDR configurations is 750 Mbps per lane.

6 Thermal characteristics

6.1 Thermal absolute maximum ratings

Caution: Stresses above those listed in the table [Table 16. Absolute maximum rating conditions](#), may cause permanent damage to the device. These are absolute maximum ratings only. Functional operation of the device is not implied at these or any other conditions beyond those specified in the operating sections of this document. Prolonged exposure to absolute maximum rating conditions may affect device reliability.

Table 16. Absolute maximum rating conditions

Parameter	Min.	Max.	Unit
Storage temperature (T_STG)	-40	+125	°C

6.2 Junction operating temperature conditions

The junction operating temperature is the temperature range within which the device can be powered and operated without damage. This specification applies to both the OBGA package version and the wafer reconstruction version.

The device includes internal thermal sensors that can be read during operation to continuously monitor the silicon temperature.

Table 17. Junction operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit
T_JF	Junction temperature (functional operation)	-30	—	85	°C

6.3 Package thermal resistance

Table 18. OBGA package thermal resistance

Parameter	Minimum	Typical	Maximum	Unit
R _{th JA} (JEDEC 2s2p PCB)	—	30	—	°C/W

7 Electrical characteristics

Unless otherwise specified:

- Typical values are quoted for nominal voltage, process, and temperature
- Maximum values are quoted for worst case conditions (process, voltage, and functional temperature)

7.1 Absolute maximum ratings

Caution: Stresses above those listed under "Absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 19. Absolute maximum ratings

Symbol	Parameter	Maximum	Unit
VANA	Analog power supply	3.99	V
VCORE	Digital core power supply	1.89	V
VDDIO	Digital I/O power supply	2.85	V
VESD, electrostatic discharge model	Human body model (HBM)	±2	kV
	Charge device model (CDM)	±500	V

7.2 Operating conditions

Table 20. Operating conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
VANA	Analog power supply	2.70	2.80	2.90	V
VCORE	Digital core power supply	1.05	1.15	1.26	
VDDIO	Digital I/O power supply	1.70	1.80	1.90	

7.3 Electrical parameters

7.3.1 Power supplies POR threshold

The device has power-on-reset (POR) detection cells with hysteresis on all power supplies. The POR is released after a typical delay of 20 μ s on the rising edge. Bursts with a duration of less than 2 μ s (typical) are ignored.

Table 21. POR threshold

Supply	Maximum threshold on rising edge	Minimum threshold on falling edge	Unit
VANA	1.33	0.84	V
VCORE	0.74	0.49	
VDDIO	1.32	0.83	

7.3.2 Power consumption

7.3.2.1 Typical streaming power consumption versus image size

Sensor common settings:

- AGAIN = 2
- Exposure time = 10 ms
- Tj = 60°C
- MIPI 1.5 Gbps
- RAW10
- EXTCLK = 25 MHz

Use case Rolling Shutter, Bayer RGB output, 50 fps, MIPI 4 lanes:

Table 22. Typical power consumption in rolling shutter mode

Resolution	VANA (mA)	VCORE (mA)	VDDIO (mA)	Total power (mW)
2560x1984	51.6	208	0.52	376
1920x1080	38	139	0.52	263
1280x720	32.6	113	0.52	220
640x480	28.7	97	0.52	191

Use case Global Shutter, NIR output, 30 fps, MIPI 2 lanes:

Table 23. Typical power consumption in global shutter mode

Resolution	VANA (mA)	VCORE (mA)	VDDIO (mA)	Total power (mW)
2560x1984	33	158	0.52	271
1920x1080	26	124	0.52	214
1280x720	21.3	111	0.52	186
640x480	19.5	103	0.52	173

7.3.2.2 Typical streaming power consumption versus frame rate

Sensor common settings:

- AGAIN = 2
- exposure time = 10ms
- Tj = 60°C
- MIPI 1.5Gbps , 4 lanes
- RAW10
- Image 2560x1984
- EXTCLK = 25 MHz

Use case Rolling Shutter, Bayer RGB output:

Table 24. Typical power consumption in rolling shutter mode

Frame rate (fps)	VANA (mA)	VCORE (mA)	VDDIO (mA)	Total power (mW)
20	32.2	126	0.52	233
30	39	153	0.52	281
40	45.5	180	0.52	330
50	51.6	208	0.52	376

Use case Global Shutter, NIR output:

Table 25. Typical power consumption in global shutter mode

Frame rate (fps)	VANA (mA)	VCORE (mA)	VDDIO (mA)	Total power (mW)
20	26	135	0.52	225
30	29	153	0.52	254
40	32.8	175	0.52	290
50	36	191	0.52	315
60	39.5	219	0.52	354
100 (exposure 9.5 ms)	53	297	0.52	475

7.3.2.3 Typical and maximum power consumption

Maximum values are quoted for worst case conditions (process, voltage, and functional temperature) and evaluated on a limited number of devices.

Typical values are quoted at nominal voltage and $T_j = 60^\circ\text{C}$.

Sensor streaming settings:

- AGAIN = 1
- Exposure time = 3 ms
- MIPI 1.3 Gbps, 4 lanes
- Global shutter NIR Smart Upscale RAW10
- Image 2560x1984
- Frame rate 60 fps
- Test pattern generator pseudo random PN28
- EXTCLK = 25 MHz
- Defect pixel correction ON
- Gaussian filter ON

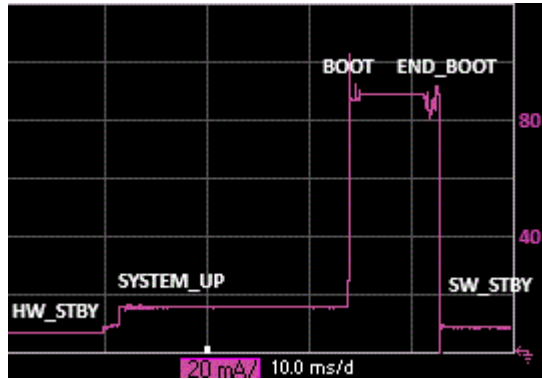
Table 26. Typical and maximum power consumption

	VANA		VCORE		VDDIO		Unit
	Typ.	Max.	Typ.	Max.	Typ.	Max.	
HW_STANDBY	0.08	0.1	9.0	45.0	0.013	0.02	mA
SW_STANDBY after BOOT	0.7	1.0	11.0	55.0	0.013	0.02	
SW_STANDBY after STREAMING	4.5	5.0	13.5	60.0	0.013	0.02	
STREAMING	38.5	40.0	222.0	290.0	0.52	0.6	

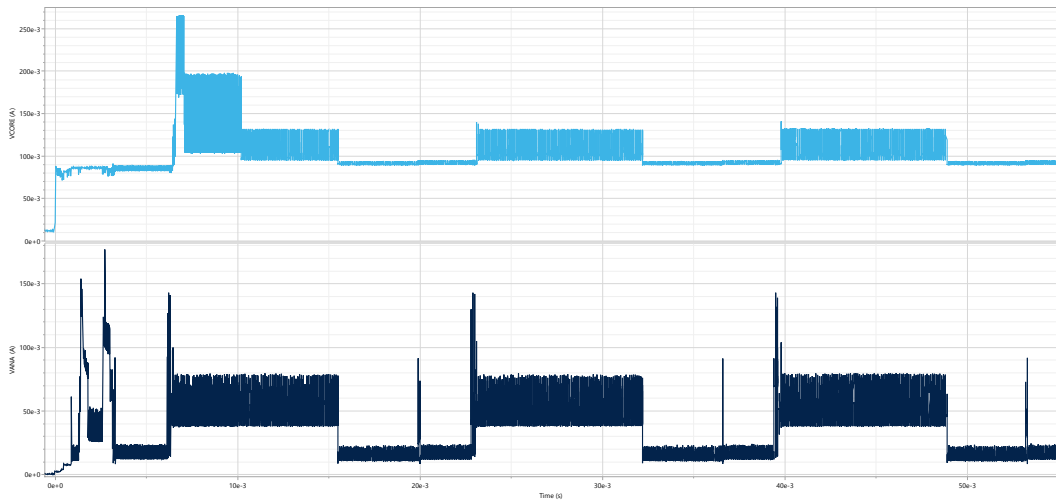
7.3.3 Current profile

BOOT sequence

The data of the figure below has been captured on one device at nominal temperature and voltage.

Figure 28. V_{CORE} transient current during BOOT

START_STREAM sequence

 Refer to [Section 7.3.2: Power consumption](#) for the streaming conditions.

Figure 29. First frames typical current profile (A) over time (s)


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7.3.4 EXTCLK input
Table 27. EXTCLK input
 $V_{EXTCLKL}$, $V_{EXTCLKH}$, f_{EXTCLK} , $C_{toCjitter}$ and duty cycle are evaluated on a limited number of devices.

Symbol	Parameter	Min.	Max.	Unit
$V_{EXTCLKL}$	DC-coupled square wave low-level input	-0.5	$0.3 \times V_{DDIO}$	V
$V_{EXTCLKH}$	DC-coupled square wave high-level input	$0.7 \times V_{DDIO}$	$V_{DDIO} + 0.5$	
f_{EXTCLK}	Clock input frequency	12	50	MHz
$C_{toCjitter}$	Clock maximum cycle to cycle jitter	—	200	ps
Duty cycle	Clock duty cycle	40	60	%
I_{EXTCLK}	Input leakage current	—	10	μA

7.3.5 Digital inputs

Table 28. Digital inputs

V_{IL} and V_{IH} are evaluated on a limited number of devices.

Symbol	Parameter	Min.	Max.	Unit
V_{IL}	Low-level input voltage	-0.5	$0.3 \times V_{DDIO}$	V
V_{IH}	High-level input voltage	$0.7 \times V_{DDIO}$	$V_{DDIO} + 0.5$	
I_{Leak}	Input leakage current ⁽¹⁾	—	10	μA

1. For $0 \leq V_I \leq V_{DDIO}$

Table 29. GPIO pull down resistance value

Symbol	Parameter	Min.	Typical	Unit
Rpd	Pull down resistance	28	50	K Ω

7.3.6 Digital outputs

Table 30. Digital outputs

Symbol	Parameter	Conditions	Min.	Max.	Unit
V_{OL}	Low-level output voltage	$I_{OL} = -4 \text{ mA}$	—	0.4	V
V_{OH}	High-level output voltage	$I_{OH} = 4 \text{ mA}$	$V_{DDIO} - 0.4$	—	
I_{max}	Maximum current		—	4	mA

7.3.7 I²C interface - SDA, SCL

I²C timing and voltage conform to the standard described in UM10204: I²C-bus specification and user manual, Rev. 6. Refer to [Appendix A: I²C interface - SDA, SCL - Norm extract](#) for further information.

It is evaluated on a limited number of devices.

Refer to [Section 5.1: Inter-integrated circuit](#) for limitation description.

7.3.8 CSI-2 interface

The CSI-2 interface conforms to the MIPI Alliance specification for D-PHY version 1.1. Refer to the standard for complete details of the specification. Refer to [Appendix B: CSI-2 interface - Specification extract](#) for further information.

The interface has been evaluated by characterization for a typical process, at ambient temperature, and with full VCORE voltage coverage (minimum/typical/maximum). The sensor has been programmed as follows:

- Resolution = Full
- Shutter mode = Rolling
- Frame rate = 30 fps
- External clock = 25 MHz
- CSI-2 data rate = 1.3 Gbps/lane
- Pattern generator = Enabled

High-speed mode - AC is evaluated on a limited number of devices.

8 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

8.1 OBGA package information

8.1.1 OBGA package dimensions

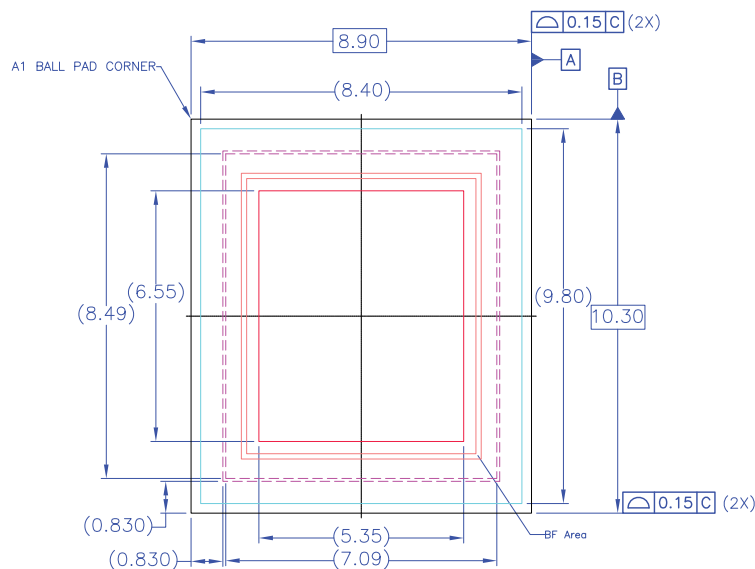
Table 31. OBGA package mechanical data

Parameter	Minimum	Typical	Maximum	Unit
Width	8.75	8.90	9.05	mm
Height	10.15	10.30	10.45	mm
Thickness	1.90	2.05	2.20	mm

- The bond line thickness (substrate to silicon interface) is 20 μm .
- The silicon die thickness is 200 μm .
- The optical center is aligned with the package center.
- The focusing plane is designed to be on the top surface of the silicon, with a height tolerance of $\pm 30 \mu\text{m}$.
- Focusing plan tilt is maximum 25 μm .
- The ball pitch is 800 μm in both directions
- The ball diameter is 520 μm

8.1.2 Mechanical drawings

Figure 30. Top view



Prerelease product(s)

Figure 31. Bottom view

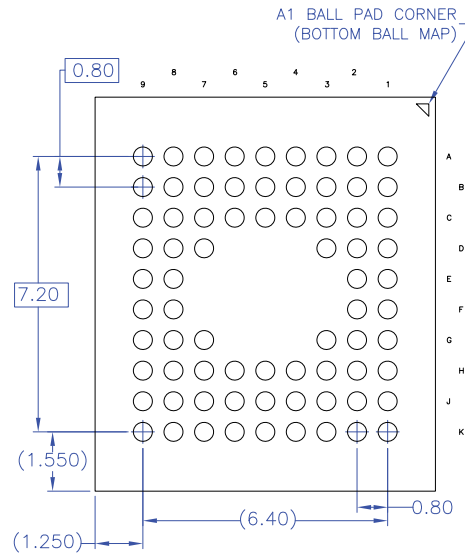
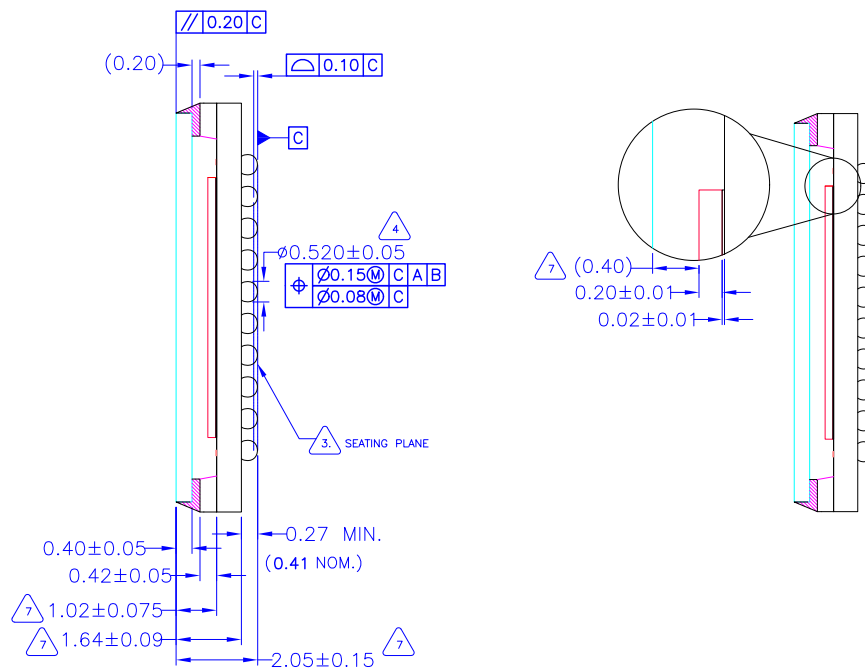


Figure 32. Side view



Note: These drawings are subject to change without notice.

Note: All linear dimensions are in millimeters.

Prerelease product(s)

8.1.3 Glass properties

Note: *In its OBGA packaged version (VB1943), the sensor is supplied without a protective liner on the glass window. Strict ESD-safe handling, use of cleanroom-compatible tools and appropriate cleanliness controls are recommended to prevent contamination, scratching, or other damage to the optical surface.*

Table 32. Glass reflectance and transmittance

Items		Requirements			
Glass optical specification		Band nm	0° ⁽¹⁾	30° ⁽¹⁾	5° ⁽¹⁾
	Transmittance (T)	900-1000	Tminimum > 97.5%	Tminimum > 97%	
	Reflectivity (R)	900-1000	—		Raverage < 1.5% Rmaximum < 2%

1. Incidence angle

8.2 Die mechanical description

8.2.1 Die dimensions

In the table below, the die dimensions are after sawing.

Table 33. Die dimensions

Parameter	Minimum	Typical	Maximum	Unit
X die (after sawing)	6536	6546	6556	µm
Y die (after sawing)	5339	5349	5359	µm
Die thickness	190	200	210	µm

8.2.2 Optical center

The reference of the optical center is the die center.

Table 34. Optical center

Parameter	X position (µm)	Y position (µm)
Optical center	0	0

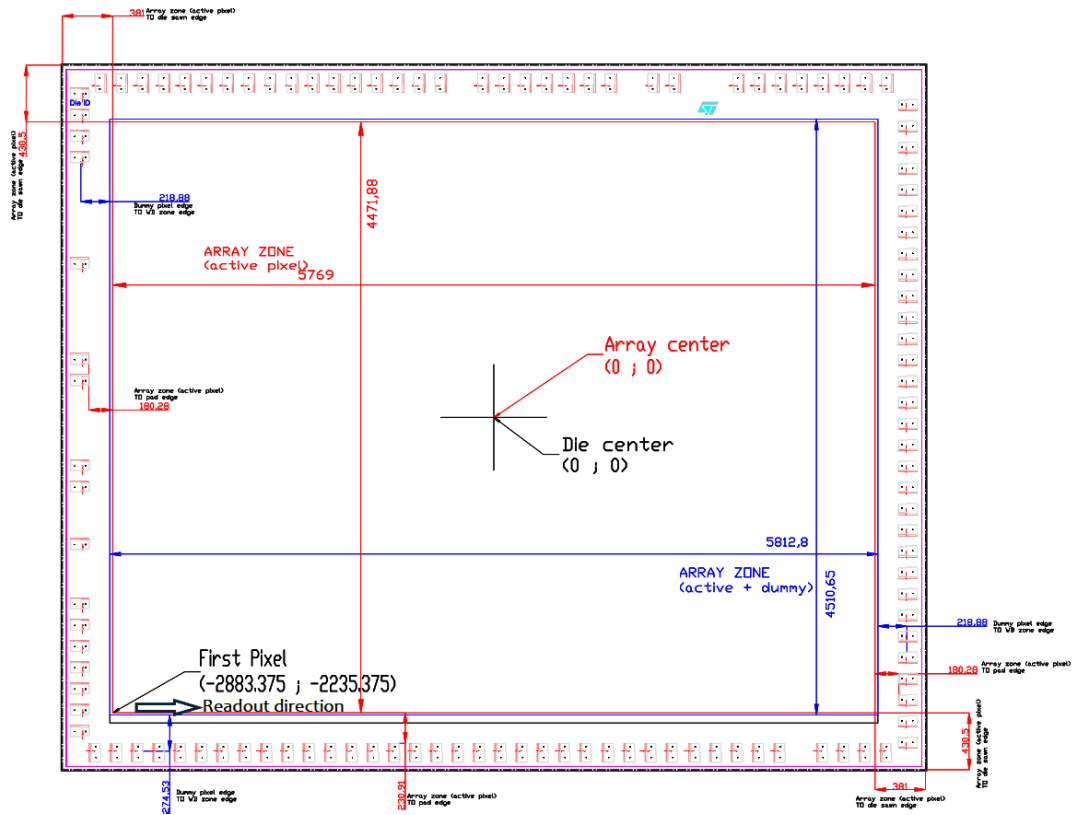
8.2.3 Die layout

See [Table 35. Pad assignment](#) for signal descriptions.

The optical area in [Figure 33](#) corresponds to the pixel matrix. This pixel matrix is surrounded by a crown of two pixels (two rows on the top, two rows on the bottom, two columns on the left, and two columns on the right). The pixels on the edge are used by the digital processing blocks for optimizing image quality. They are not transmitted by the sensor, although they are considered for designing the optical stack of the camera module.

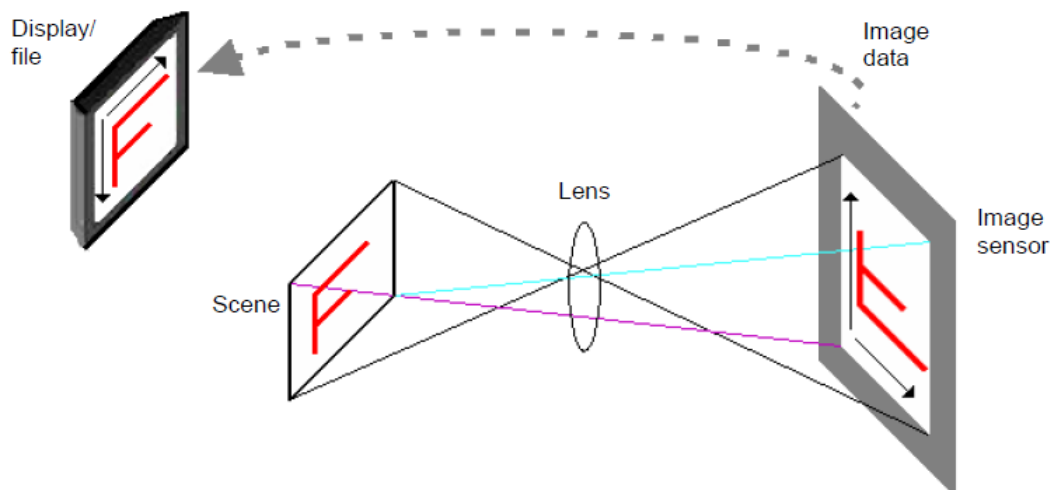
The extended zone in [Figure 33](#) corresponds to all pixels of the matrix, plus dummy and dark pixels. Dummy and dark pixels are exclusively processed internally. Do not consider them for designing the optical stack.

Figure 33. Die pad positions (see-through view)



The actual image of the scene projected through the lens onto the pixel array means that it is necessary to read the array starting at the bottom-left corner. This is so that the final displayed image is correct (refer to the arrow "Read OUT" in Figure 33).

Figure 34. Image orientation



As this document is related to the die, the image orientation (depicted by an "F" symbol) shows the image as it is really being captured by the sensor. The pixel readout is fully programmable (mirror and flip) but the default read fashion is from left to right and bottom to top as shown in Figure 34. Image orientation.

Prerelease product(s)

8.2.4 Pad assignment

The following assignment is listed from top left of the die in a clockwise direction.

Table 35. Pad assignment

Pad number	Side	Pin name	Bonding point, X co-ordinate	Bonding point, Y co-ordinate
1	Top	VANA	-2983.99	2569.61
2	Top	VANA	-2822.97	2569.61
3	Top	VANA	-2661.94	2569.61
4	Top	AGND	-2500.91	2569.61
5	Top	AGND	-2339.88	2569.61
6	Top	CPPOS_OUT	-2178.86	2569.61
7	Top	CPPOS_IN	-2017.83	2569.61
8	Top	AGND	-1856.8	2569.61
9	Top	VCORE	-1695.77	2569.61
10	Top	DGND	-1534.74	2569.61
11	Top	VCORE	-1373.72	2569.61
12	Top	DGND	-1212.69	2569.61
13	Top	VANA	-1051.66	2569.61
14	Top	VANA	-890.63	2569.61
15	Top	AGND	-729.6	2569.61
16	Top	DGND	-568.58	2569.61
17	Top	VRT	-407.55	2569.61
18	Top	AGND	-85.49	2569.61
19	Top	VCORE	75.54	2569.61
20	Top	VCORE	236.57	2569.61
21	Top	DGND	397.59	2569.61
22	Top	AGND	558.62	2569.61
23	Top	VANA	719.65	2569.61
24	Top	VANA	880.68	2569.61
25	Top	DGND	1202.730	2569.61
26	Top	AGND	1363.76	2569.61
27	Top	VANA	1846.85	2569.61
28	Top	DGND	2007.87	2569.61
29	Top	VCORE	2168.9	2569.61
30	Top	VCORE	2329.93	2569.61
31	Top	AGND	2490.96	2569.61
32	Top	VANA	2651.99	2569.61
33	Top	AGND	2813.01	2569.61
34	Top	VCORE	2974.04	2569.61
35	Right	DGND	3168.11	2374.78
36	Right	VANA	3168.11	2213.76
37	Right	AGND	3168.11	2052.73

Prerelease product(s)

Pad number	Side	Pin name	Bonding point, X co-ordinate	Bonding point, Y co-ordinate
38	Right	VDDIO	3168.11	1891.7
39	Right	DGND	3168.11	1730.67
40	Right	VCORE	3168.11	1569.64
41	Right	NC	3168.11	1408.62
42	Right	NC	3168.11	1247.59
43	Right	DGND	3168.11	1086.56
44	Right	VDDIO	3168.11	925.53
45	Right	DGND	3168.11	764.51
46	Right	EXTCLK	3168.11	603.48
47	Right	VCORE	3168.11	442.45
48	Right	DGND	3168.11	281.42
49	Right	VANA	3168.11	120.39
50	Right	VANA	3168.11	-40.63
51	Right	AGND	3168.11	-201.66
52	Right	LDO2V4	3168.11	-362.69
53	Right	DGND	3168.11	-523.72
54	Right	VCORE	3168.11	-684.75
55	Right	DGND	3168.11	-845.77
56	Right	DATA4P	3168.11	-1006.8
57	Right	DATA4N	3168.11	-1167.83
58	Right	DATA1P	3168.11	-1328.86
59	Right	DATA1N	3168.11	-1489.89
60	Right	CLKP	3168.11	-1650.91
61	Right	CLKN	3168.11	-1811.94
62	Right	DATA2P	3168.11	-1972.97
63	Right	DATA2N	3168.11	-2134
64	Right	DATA3P	3168.11	-2295.03
65	Right	DATA3N	3168.11	-2456.06
66	Bottom	NC	2974.04	-2569.61
67	Bottom	DGND	2813.01	-2569.61
68	Bottom	VCORE	2651.99	-2569.61
69	Bottom	AGND	2490.96	-2569.61
70	Bottom	AGND	2168.9	-2569.61
71	Bottom	VCORE	2007.87	-2569.61
72	Bottom	DGND	1846.85	-2569.61
73	Bottom	PORTEST (must be grounded)	1685.82	-2569.61
74	Bottom	NC	1524.79	-2569.61
75	Bottom	VDDIO	1353.56	-2569.61
76	Bottom	NC	1192.53	-2569.61
77	Bottom	DGND	1031.5	-2569.61

Pad number	Side	Pin name	Bonding point, X co-ordinate	Bonding point, Y co-ordinate
78	Bottom	VCORE	870.47	-2569.61
79	Bottom	DGND	699.24	-2569.61
80	Bottom	RESETN	538.21	-2569.61
81	Bottom	GPIO0	377.18	-2569.61
82	Bottom	GPIO1	216.15	-2569.61
83	Bottom	VCORE	55.13	-2569.61
84	Bottom	GPIO2	-105.9	-2569.61
85	Bottom	GPIO3	-266.93	-2569.61
86	Bottom	DGND	-427.96	-2569.61
87	Bottom	VDDIO	-588.99	-2569.61
88	Bottom	DGND	-750.02	-2569.61
89	Bottom	SDA	-911.04	-2569.61
90	Bottom	SCL	-1072.07	-2569.61
91	Bottom	CLK_RANGE0	-1233.1	-2569.61
92	Bottom	CLK_RANGE1	-1394.13	-2569.61
93	Bottom	VCORE	-1555.15	-2569.61
94	Bottom	NC	-1716.18	-2569.61
95	Bottom	NC	-1877.21	-2569.61
96	Bottom	AGND	-2048.45	-2569.61
97	Bottom	NC	-2209.47	-2569.61
98	Bottom	NC	-2370.5	-2569.61
99	Bottom	VANA	-2531.53	-2569.61
100	Bottom	DGND	-2692.56	-2569.61
101	Bottom	VCORE	-2853.59	-2569.61
102	Bottom	AGND	-3014.61	-2569.61
103	Left	CPNEG_OUT	-3168.11	-2375.54
104	Left	CPNEG_IN	-3168.11	-2214.51
105	Left	AGND	-3168.11	-2053.49
106	Left	AGND	-3168.11	-1892.46
107	Left	VANA	-3168.11	-1731.43
108	Left	VANA	-3168.11	-1570.4
109	Left	AGND	-3168.11	-1409.370
110	Left	NC	-3168.11	-959.430
111	Left	DGND	-3168.11	-523.72
112	Left	VANA	-3168.11	-362.69
113	Left	AGND	-3168.11	281.42
114	Left	VCORE	-3168.11	442.45
115	Left	AGND	-3168.11	1167.08
116	Left	VANA	-3168.11	1972.97
117	Left	DGND	-3168.11	2134

Pad number	Side	Pin name	Bonding point, X co-ordinate	Bonding point, Y co-ordinate
118	Left	VCORE	-3168.11	2295.03
119	Left	AGND	-3168.11	2456.06

8.2.5 Bonding pad information

Figure 35. Bonding pad opening

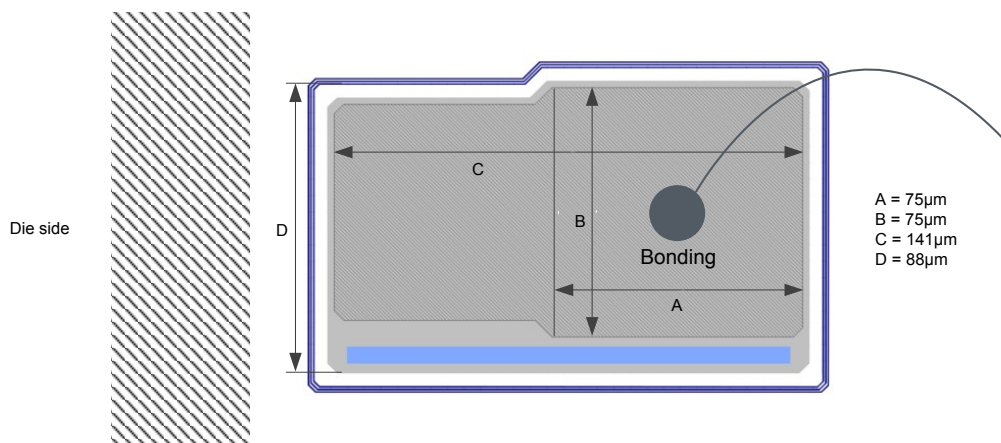


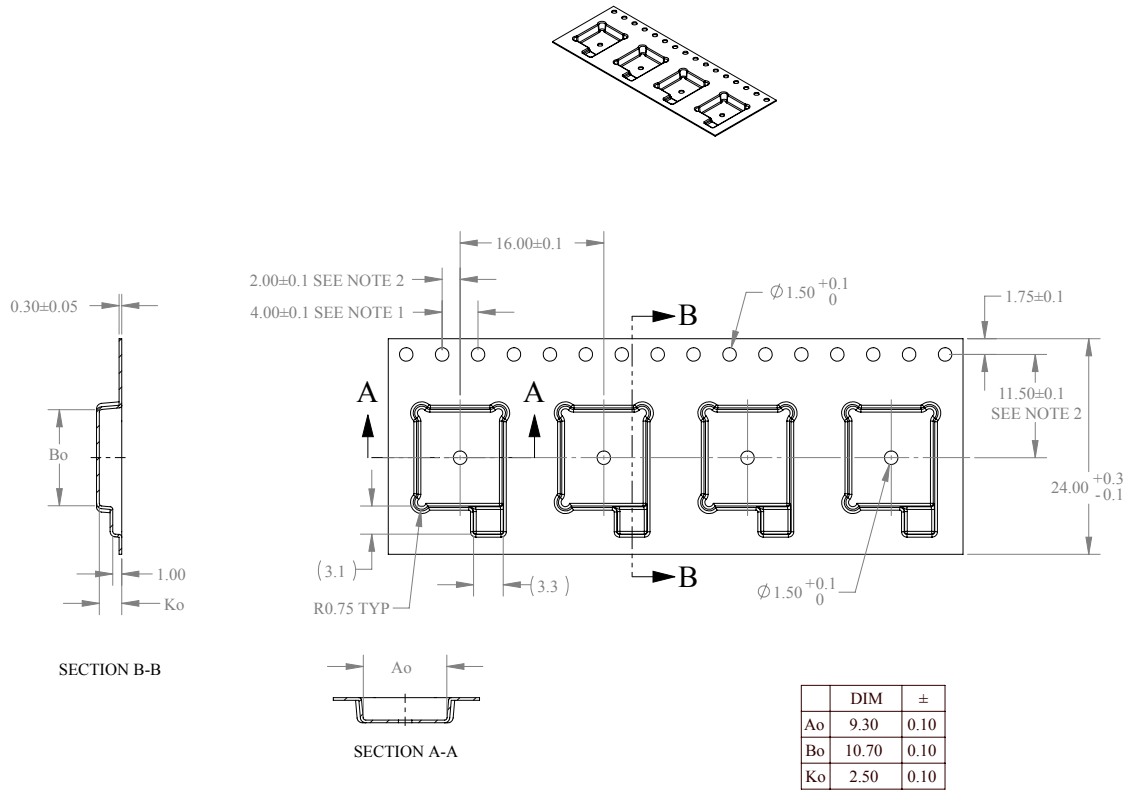
Table 36. Pad opening size

Parameter	X (µm)	Y (µm)
Pad opening size	75	75

9.1.2 Tape and reel information

The carrier tape is wound onto a reel.

Figure 37. Carrier tape

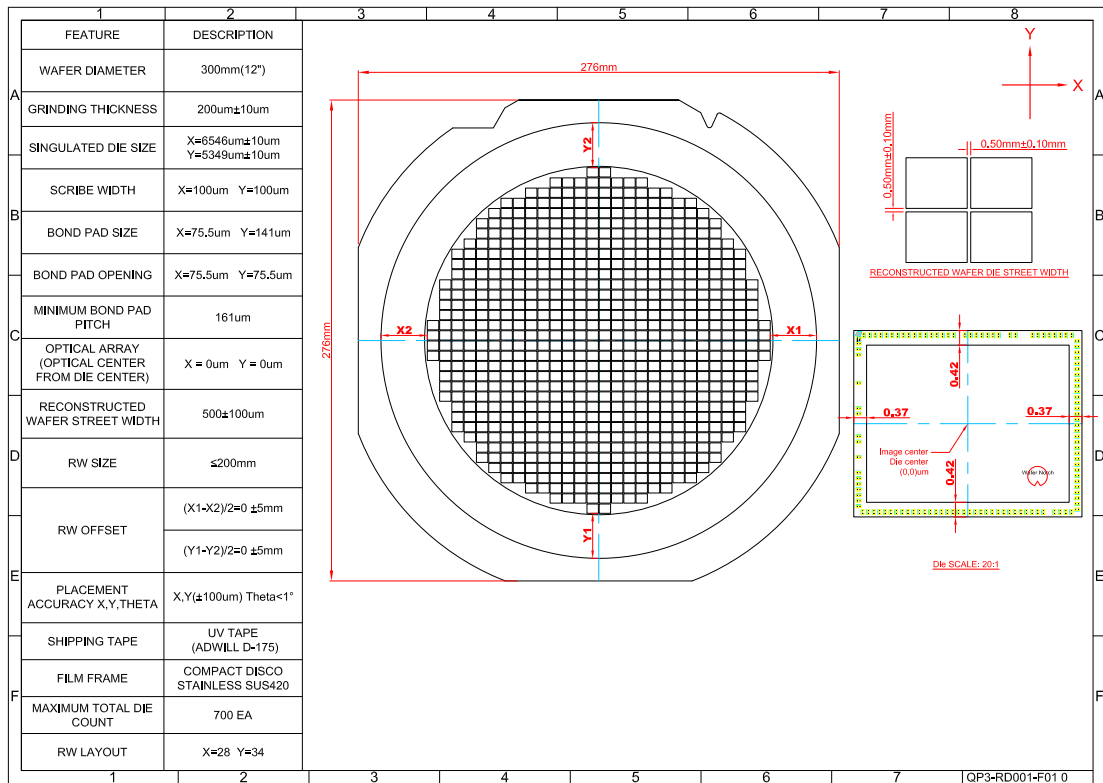


Prerelease product(s)

9.2 Packing

Tested dice are delivered as sawn dice which are reconstructed into a wafer format on UV-tape, and delivered on a metallic ring (see figure below). The frames are packed in plastic containers, each including a maximum of 13 double-spaced reconstructed wafer rings. A mapping information file is also provided for localizing dice that may have been damaged during wafer reconstruction on sticking foil.

Figure 38. Reconstructed wafer information



Prerelease product(s)

9.3 Storage conditions

The parts must be stored in a sealed bag for a maximum of 24 months at <40°C and <90% relative humidity (RH).

10 Handling, moisture, and reflow profile

10.1 Storage conditions

Store all packing material in an appropriate indoor area. This is to prevent any dust and/or damage from the sun, external light, and physical shocks.

Keep the temperature between 15°C and 35°C, with a relative humidity range between 10% and 70% maximum.

Refer to the Technical Note TN1497, Reconstructed wafer specifications for visual inspection and packing for additional information.

10.2 Soldering information

The OBGA package is compliant with the RoHS and “green” standards and is qualified for soldering heat resistance according to JEDEC J-STD-020.

Figure 39. Soldering temperature vs time

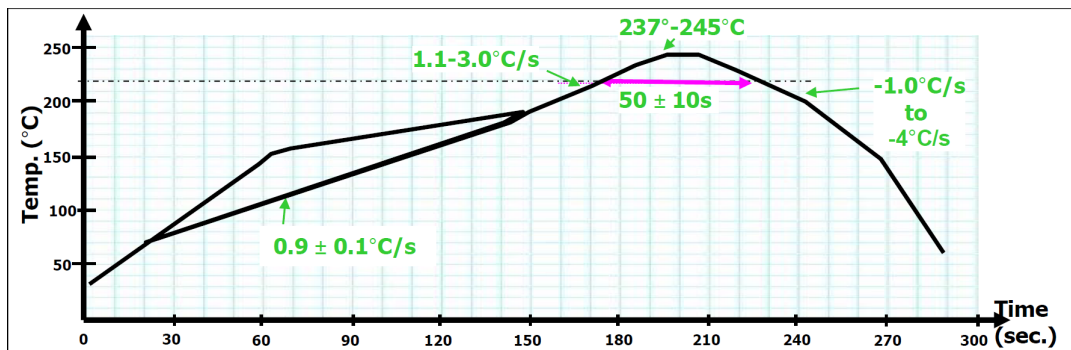


Table 37. Soldering details

Profile	Ramp to strike
Temperature gradient in preheat (T = 70-180°C)	0.9 ± 0.1°C/s
Temperature gradient (T = 200-225°C)	1.1 - 3.0°C/s
Peak temperature in reflow	237°C - 245°C
Time above 220°C	50 ± 10 s
Temperature gradient in cooling	-1 to -4°C/s (-6°C/s max.)
Temperature from 50°C to 220°C	160 to 220 s

11 Ordering information

Table 38. Order code

Order code	Pixel type	Resolution (MPixel)	Package	Packing
VB1943CAJX	RGB NIR	5.1	OBGA	Tray
VB1943CAJX/1				Tape and reel
VD1943CE/RW			Bare die	Reconstructed wafer

12 Acronyms and abbreviations

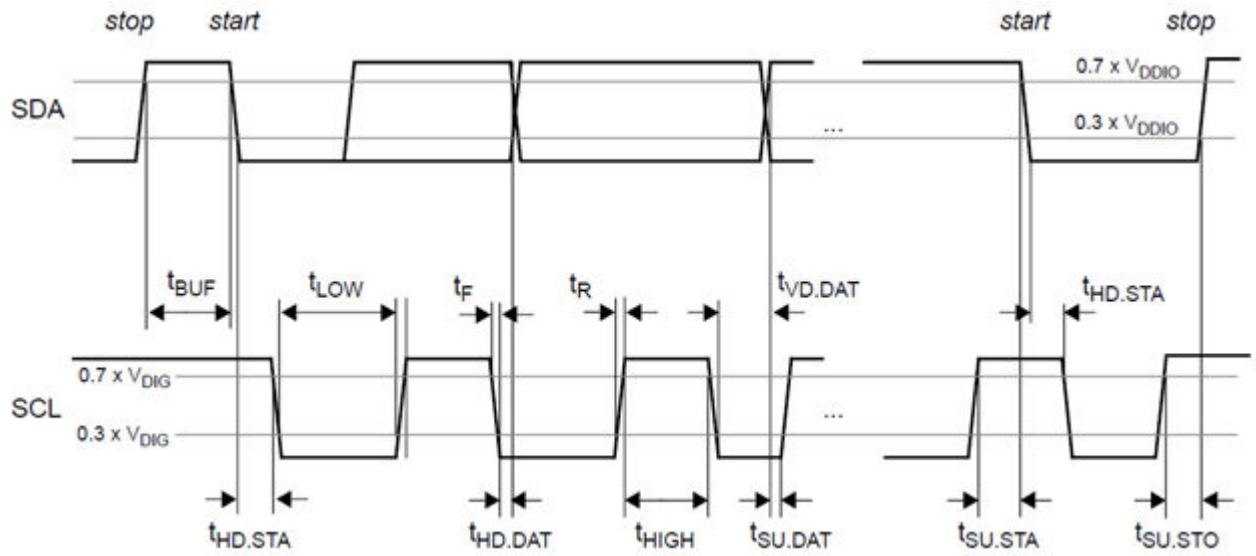
Table 39. Acronyms and abbreviations

Acronym/abbreviation	Definition
ADC	Analog-to-digital converter
BIST	built-in self-test
BSI	backside illumination
CAB	custom analog block
CCI	camera control interface
CPU	central processing unit
CRA	chief ray angle
CRC	cyclic redundancy check
CSI	camera serial interface
DAC	Digital-to-analog converter
ECC	error correction code
EMC	electromagnetic compatibility
EMI	electromagnetic interference
FoV	field of view
fps	frames per second
GPIO	General-purpose input/output
HDR	high dynamic range
ISL	intelligent status line
ISP	image signal processor
I ² C	Inter-integrated circuit (bus)
NIR	near infrared
OIF	output interface
OTP	one-time programmable
PLL	phase-locked loop
PWL	piecewise linear
PWM	pulse-width modulation
RGB	red green blue
ROM	read-only memory
SCL	serial clock (for I ² C)
SDA	serial data (for I ² C)
SDR	standard dynamic range
UI	user interface
SOC	system on chip
MCU	microcontroller unit
MPU	microprocessor unit

Appendix A I²C interface - SDA, SCL - Norm extract

Figure 40. I²C timing

The values below are for all process, voltage, and temperature conditions.



Prerelease product(s)

Appendix B CSI-2 interface - Specification extract

DC specification

The DC specifications are evaluated by characterization for all process, voltage, and temperature conditions. They are not tested in production.

Table 40. CSI-2 interface - high-speed mode - DC specifications

Symbol	Parameter	Min	Typical	Max	Unit
V_{CMTX}	HS transmits static common-mode voltage	150	200	250	mV
V_{OD}	HS transmits differential voltage ⁽¹⁾	140	200	270	
V_{OHHS}	HS outputs high voltage ⁽²⁾	—	—	360	
Z_{OS}	Single-ended output impedance	40	50	62.5	Ω

1. Value when driving into load impedance anywhere in the ZID range (80-125 Ω)
2. Characterization data only

Table 41. CSI-2 interface - low-power mode - DC specifications

Symbol	Parameter	Min	Typical	Max	Unit
V_{OH}	Output high-level	1.1	1.2	1.3	V
V_{OL}	Output low-level	-50	—	50	mV
Z_{OLP}	Output impedance of LP transmitter	110	—	—	Ω

AC specification

Table 42. CSI-2 interface - high-speed mode - AC specifications

Symbol	Parameter	Min.	Typ.	Max.	Unit
—	Data rate	250	804	1500	Mbit/s
t_{clkp}	Average data period	—	1.25	—	ns
t_r and t_f	t_f 20% - 80% rise time and fall time	100	—	0.3UI	ps
t_{skew}	Data-to-clock skew	-0.15UI	—	0.15UI	

Revision history

Table 43. Document revision history

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09-Apr-2026	1	Initial release

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